Kinetis KL05 32 KB Flash

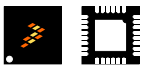
48 MHz Cortex-M0+ Based Microcontroller

MKL05ZxxVFK4
MKL05ZxxVLC4
MKL05ZxxVFM4
MKL05ZxxVLF4

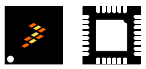
Designed with efficiency in mind. Features a size efficient, small package, energy efficient ARM Cortex-M0+ 32-bit performance. Shares the comprehensive enablement and scalability of the Kinetis family.

This product offers:

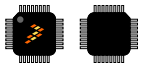
- Run power consumption down to 45 µA/MHz in very low power run mode
- Static power consumption down to 2 µA with full state retention and 4 µs wakeup
- Ultra-efficient Cortex-M0+ processor running up to 48MHz with industry leading throughput
- Memory option is up to 32 KB Flash and 4 KB RAM
- Energy-saving architecture is optimized for low power with 90 nm TFS technology, clock and power gating techniques, and zero wait state flash memory controller



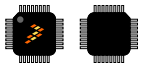
24-pin QFN (FK)
4 x 4 x 1 Pitch 0.5 mm



32-pin QFN (FM)
5 x 5 x 1 Pitch 0.5 mm



32-pin LQFP (LC)
7 x 7 x 1.4 Pitch 0.8 mm



48-pin LQFP (LF)
7 x 7 x 1.4 Pitch 0.5 mm

Performance

- 48 MHz ARM® Cortex®-M0+ core

Memories and memory interfaces

- Up to 32 KB program flash memory
- Up to 4 KB SRAM

System peripherals

- Nine low-power modes to provide power optimization based on application requirements
- COP Software watchdog
- 4-channel DMA controller, supporting up to 63 request sources
- Low-leakage wakeup unit
- SWD debug interface and Micro Trace Buffer
- Bit Manipulation Engine

Clocks

- 32 kHz to 40 kHz or 3 MHz to 32 MHz crystal oscillator
- Multi-purpose clock source
- 1 kHz LPO clock

Operating Characteristics

- Voltage range: 1.71 to 3.6 V
- Flash write voltage range: 1.71 to 3.6 V
- Temperature range (ambient): -40 to 105°C

Human-machine interface

- Low-power hardware touch sensor interface (TSI)
- Up to 41 general-purpose input/output (GPIO)

Communication interfaces

- One 8-bit SPI module
- One low power UART module
- One I2C module

Analog Modules

- 12-bit SAR ADC
- 12-bit DAC
- Analog comparator (CMP) containing a 6-bit DAC and programmable reference input

Timers

- Six channel Timer/PWM (TPM)
- One 2-channel Timer/PWM module
- Periodic interrupt timers
- 16-bit low-power timer (LPTMR)
- Real time clock

Security and integrity modules

- 80-bit unique identification number per chip

Ordering Information

Part Number	Memory		Maximum number of I\O's
	Flash (KB)	SRAM (KB)	
MKL05Z8VFK4	8	1	22
MKL05Z16VFK4	16	2	22
MKL05Z32VFK4	32	4	22
MKL05Z8VLC4	8	1	28
MKL05Z16VLC4	16	2	28
MKL05Z32VLC4	32	4	28
MKL05Z8VFM4	8	1	28
MKL05Z16VFM4	16	2	28
MKL05Z32VFM4	32	4	28
MKL05Z16VLF4	16	2	41
MKL05Z32VLF4	32	4	41

Related Resources

Type	Description
Selector Guide	The Freescale Solution Advisor is a web-based tool that features interactive application wizards and a dynamic product selector.
Product Brief	The Product Brief contains concise overview/summary information to enable quick evaluation of a device for design suitability.
Reference Manual	The Reference Manual contains a comprehensive description of the structure and function (operation) of a device.
Data Sheet	The Data Sheet includes electrical characteristics and signal connections.
Chip Errata	The chip mask set Errata provides additional or corrective information for a particular device mask set.
Package drawing	Package dimensions are provided in package drawings.

Table of Contents

1 Ratings

1.1 Thermal handling ratings

Table 1. Thermal handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
T_{STG}	Storage temperature	–55	150	°C	1
T_{SDR}	Solder temperature, lead-free	—	260	°C	2

1. Determined according to JEDEC Standard JESD22-A103, *High Temperature Storage Life*.
2. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.2 Moisture handling ratings

Table 2. Moisture handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
MSL	Moisture sensitivity level	—	3	—	1

1. Determined according to IPC/JEDEC Standard J-STD-020, *Moisture/Reflow Sensitivity Classification for Nonhermetic Solid State Surface Mount Devices*.

1.3 ESD handling ratings

Table 3. ESD handling ratings

Symbol	Description	Min.	Max.	Unit	Notes
V_{HBM}	Electrostatic discharge voltage, human body model	–2000	+2000	V	1
V_{CDM}	Electrostatic discharge voltage, charged-device model	–500	+500	V	2
I_{LAT}	Latch-up current at ambient temperature of 105 °C	–100	+100	mA	3

1. Determined according to JEDEC Standard JESD22-A114, *Electrostatic Discharge (ESD) Sensitivity Testing Human Body Model (HBM)*.
2. Determined according to JEDEC Standard JESD22-C101, *Field-Induced Charged-Device Model Test Method for Electrostatic-Discharge-Withstand Thresholds of Microelectronic Components*.
3. Determined according to JEDEC Standard JESD78, *IC Latch-Up Test*.

1.4 Voltage and current operating ratings

Table 4. Voltage and current operating ratings

Symbol	Description	Min.	Max.	Unit
V_{DD}	Digital supply voltage	–0.3	3.8	V
I_{DD}	Digital supply current	—	120	mA
V_{IO}	IO pin input voltage	–0.3	V_{DD} + 0.3	V
I_D	Instantaneous maximum current single pin limit (applies to all port pins)	–25	25	mA
V_{DDA}	Analog supply voltage	V_{DD} – 0.3	V_{DD} + 0.3	V

2 General

2.1 AC electrical characteristics

Unless otherwise specified, propagation delays are measured from the 50% to the 50% point, and rise and fall times are measured at the 20% and 80% points, as shown in the following figure.

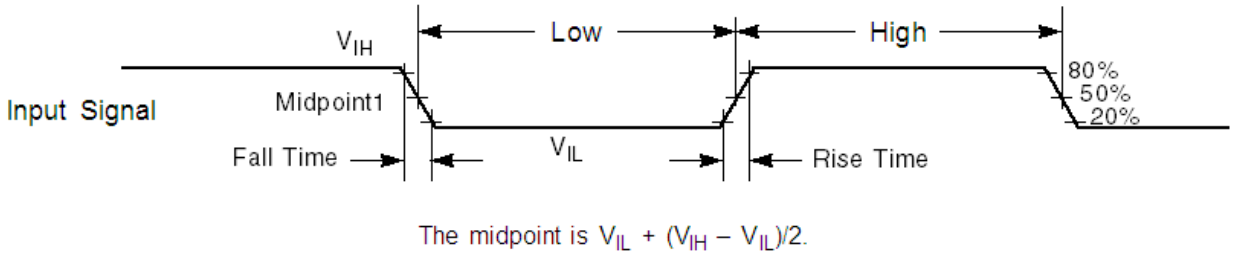


Figure 1. Input signal measurement reference

All digital I/O switching characteristics, unless otherwise specified, assume the output pins have the following characteristics.

- C_L=30 pF loads
- Slew rate disabled
- Normal drive strength

2.2 Nonswitching electrical specifications

2.2.1 Voltage and current operating requirements

Table 5. Voltage and current operating requirements

Symbol	Description	Min.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	3.6	V	
V_{DDA}	Analog supply voltage	1.71	3.6	V	—
$V_{DD} – V_{DDA}$	V_{DD}-to-V_{DDA} differential voltage	–0.1	0.1	V	—
$V_{SS} – V_{SSA}$	V_{SS}-to-V_{SSA} differential voltage	–0.1	0.1	V	—
V_{IH}	Input high voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 0.7 × V_{DD} 0.75 × V_{DD}	 — —	 V V	—
V_{IL}	Input low voltage • 2.7 V ≤ V_{DD} ≤ 3.6 V • 1.7 V ≤ V_{DD} ≤ 2.7 V	 — —	 0.35 × V_{DD} 0.3 × V_{DD}	 V V	—
V_{HYS}	Input hysteresis	0.06 × V_{DD}	—	V	—
I_{ICIO}	IO pin negative DC injection current—single pin • V_{IN} < V_{SS}–0.3V (negative current injection) • V_{IN} < V_{SS}–0.3V (positive current injection)	 –3 —	 — +3	 mA	1
I_{ICcont}	Contiguous pin DC injection current —regional limit, includes sum of negative injection currents or sum of positive injection currents of 16 contiguous pins • Negative current injection • Positive current injection	 –25 —	 — +25	 mA	—
V_{ODPU}	Open drain pullup voltage level	V_{DD}	V_{DD}	V	2
V_{RAM}	V_{DD} voltage required to retain RAM	1.2	—	V	—

1. All IO pins are internally clamped to V_{SS} and V_{DD} through ESD protection diodes. If V_{IN} is greater than V_{IO_MIN} (=V_{SS}-0.3V) and V_{IN} is less than V_{IO_MAX}(=V_{DD}+0.3V) is observed, then there is no need to provide current limiting resistors at the pads. If these limits cannot be observed then a current limiting resistor is required. The negative DC injection current limiting resistor is calculated as R=(V_{IO_MIN}-V_{IN})/|I_{ICIO}|. The positive injection current limiting resistor is calculated as R=(V_{IN}-V_{IO_MAX})/|I_{ICIO}|. Select the larger of these two calculated resistances.
2. Open drain outputs must be pulled to V_{DD}.

2.2.2 LVD and POR operating requirements

Table 6. V_{DD} supply LVD and POR operating requirements

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{POR}	Falling V_{DD} POR detect voltage	0.8	1.1	1.5	V	—
V_{LVDH}	Falling low-voltage detect threshold — high range (LVDV = 01)	2.48	2.56	2.64	V	—
	Low-voltage warning thresholds — high range					1

Table continues on the next page...

Table 6. V_{DD} supply LVD and POR operating requirements (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{LVW1H}	• Level 1 falling (LVWV = 00)	2.62	2.70	2.78	V	
V_{LVW2H}	• Level 2 falling (LVWV = 01)	2.72	2.80	2.88	V	
V_{LVW3H}	• Level 3 falling (LVWV = 10)	2.82	2.90	2.98	V	
V_{LVW4H}	• Level 4 falling (LVWV = 11)	2.92	3.00	3.08	V	
V_{HYSH}	Low-voltage inhibit reset/recover hysteresis — high range	—	±60	—	mV	—
V_{LVDL}	Falling low-voltage detect threshold — low range (LVDV=00)	1.54	1.60	1.66	V	—
	Low-voltage warning thresholds — low range					1
V_{LVW1L}	• Level 1 falling (LVWV = 00)	1.74	1.80	1.86	V	
V_{LVW2L}	• Level 2 falling (LVWV = 01)	1.84	1.90	1.96	V	
V_{LVW3L}	• Level 3 falling (LVWV = 10)	1.94	2.00	2.06	V	
V_{LVW4L}	• Level 4 falling (LVWV = 11)	2.04	2.10	2.16	V	
V_{HYSL}	Low-voltage inhibit reset/recover hysteresis — low range	—	±40	—	mV	—
V_{BG}	Bandgap voltage reference	0.97	1.00	1.03	V	—
t_{LPO}	Internal low power oscillator period — factory trimmed	900	1000	1100	µs	—

1. Rising thresholds are falling threshold + hysteresis voltage

2.2.3 Voltage and current operating behaviors

Table 7. Voltage and current operating behaviors

Symbol	Description	Min.	Max.	Unit	Notes
V_{OH}	Output high voltage — Normal drive pad (except $\overline{\text{RESET}}$)				1, 2
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = –5 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = –1.5 mA	V_{DD} – 0.5	—	V	
V_{OH}	Output high voltage — High drive pad (except RESET_b)				1, 2
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OH} = –18 mA	V_{DD} – 0.5	—	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OH} = –6 mA	V_{DD} – 0.5	—	V	
I_{OHT}	Output high current total for all ports	—	100	mA	
V_{OL}	Output low voltage — Normal drive pad				1
	• 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 5 mA	—	0.5	V	
	• 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 1.5 mA	—	0.5	V	

Table continues on the next page...

Table 7. Voltage and current operating behaviors (continued)

Symbol	Description	Min.	Max.	Unit	Notes
V_{OL}	Output low voltage — High drive pad • 2.7 V ≤ V_{DD} ≤ 3.6 V, I_{OL} = 18 mA • 1.71 V ≤ V_{DD} ≤ 2.7 V, I_{OL} = 6 mA	 — —	 0.5 0.5	 V V	1
I_{OLT}	Output low current total for all ports	—	100	mA	
I_{IN}	Input leakage current (per pin) for full temperature range	—	1	µA	3
I_{IN}	Input leakage current (per pin) at 25 °C	—	0.025	µA	3
I_{IN}	Input leakage current (total all pins) for full temperature range	—	41	µA	3
I_{OZ}	Hi-Z (off-state) leakage current (per pin)	—	1	µA	
R_{PU}	Internal pullup resistors	20	50	kΩ	4

1. PTA12, PTA13, PTB0 and PTB1 I/O have both high drive and normal drive capability selected by the associated PTx_PCRn[DSE] control bit. All other GPIOs are normal drive only.
2. The reset pin only contains an active pull down device when configured as the RESET signal or as a GPIO. When configured as a GPIO output, it acts as a pseudo open drain output.
3. Measured at V_{DD} = 3.6 V
4. Measured at V_{DD} supply voltage = V_{DD} min and Vinput = V_{SS}

2.2.4 Power mode transition operating behaviors

All specifications except t_{POR} and VLLSx→RUN recovery times in the following table assume this clock configuration:

- CPU and system clocks = 48 MHz
- Bus and flash clock = 24 MHz
- FEI clock mode

POR and VLLSx→RUN recovery use FEI clock mode at the default CPU and system frequency of 21 MHz, and a bus and flash clock frequency of 10.5 MHz.

Table 8. Power mode transition operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	
t_{POR}	After a POR event, amount of time from the point V_{DD} reaches 1.8 V to execution of the first instruction across the operating temperature range of the chip.	—	—	300	µs	1
	• VLLS0 → RUN	—	95	115	µs	
	• VLLS1 → RUN					

Table continues on the next page...

Table 8. Power mode transition operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	
		—	93	115	µs	
	• VLLS3 → RUN	—	42	53	µs	
	• LLS → RUN	—	4	4.6	µs	
	• VLPS → RUN	—	4	4.4	µs	
	• STOP → RUN	—	4	4.4	µs	

1. Normal boot (FTFA_FOPT[LPBOOT]=11).

2.2.5 Power consumption operating behaviors

The maximum values stated in the following table represent characterized results equivalent to the mean plus three times the standard deviation (mean + 3 sigma).

Table 9. Power consumption operating behaviors

Symbol	Description	Min.	Typ.	Max.[1]	Unit	Notes
I_{DDA}	Analog supply current	—	—	See note	mA	2
I_{DD_RUNCO}	Run mode current in compute operation - 48 MHz core / 24 MHz flash / bus clock disabled, code of while(1) loop executing from flash • at 3.0 V	—	4.0	4.3	mA	3
I_{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks disabled, code executing from flash • at 3.0 V	—	4.9	5.3	mA	3
I_{DD_RUN}	Run mode current - 48 MHz core / 24 MHz bus and flash, all peripheral clocks enabled, code executing from flash • at 3.0 V • at 25 °C • at 125 °C	— —	5.7 6.0	5.8 6.2	mA	3, 4
I_{DD_WAIT}	Wait mode current - core disabled / 48 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	2.7	2.9	mA	3

Table continues on the next page...

Table 9. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.[1]	Unit	Notes
I_{DD_WAIT}	Wait mode current - core disabled / 24 MHz system / 24 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	2.2	2.3	mA	3
I_{DD_PSTOP2}	Stop mode current with partial stop 2 clocking option - core and system disabled / 10.5 MHz bus / flash disabled (flash doze enabled) • at 3.0 V	—	1.5	1.7	mA	3
I_{DD_VLPRCO}	Very-low-power run mode current in compute operation - 4 MHz core / 0.8 MHz flash / bus clock disabled, code executing from flash • at 3.0 V	—	182	253	µA	5
I_{DD_VLPR}	Very low power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks disabled, code executing from flash • at 3.0 V	—	213	284	µA	5
I_{DD_VLPR}	Very low power run mode current - 4 MHz core / 0.8 MHz bus and flash, all peripheral clocks enabled, code executing from flash • at 3.0 V	—	243	313	µA	4, 5
I_{DD_VLPW}	Very low power wait mode current - core disabled / 4 MHz system / 0.8 MHz bus / flash disabled (flash doze enabled), all peripheral clocks disabled • at 3.0 V	—	111	170	µA	5
I_{DD_STOP}	Stop mode current • at 3.0 V • at 25 °C • at 50 °C • at 70 °C • at 85 °C • at 105 °C	 — — — — —	 257 265 278 295 353	 277 285 303 326 412	µA	
I_{DD_VLPS}	Very-low-power stop mode current • at 3.0 V • at 25 °C • at 50 °C • at 70 °C • at 85 °C • at 105 °C	 — — — — —	 2.25 4.08 8.10 14.18 37.07	 5.76 8.27 14.52 23.78 58.58	µA	
I_{DD_LLS}	Low-leakage stop mode current • at 3.0 V					

Table continues on the next page...

Table 9. Power consumption operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.[1]	Unit	Notes
	• at 25 °C	—	1.72	2.01	µA	
	• at 50 °C	—	2.52	3.18		
	• at 70 °C	—	4.32	5.94		
	• at 85 °C	—	7.18	10.00		
	• at 105 °C	—	18.67	25.65		
I_{DD_VLLS3}	Very-low-leakage stop mode 3 current • at 3.0 V				µA	
	• at 25 °C	—	1.16	1.36		
	• at 50 °C	—	1.78	2.27		
	• at 70 °C	—	3.23	4.38		
	• at 85 °C	—	5.57	7.53		
	• at 105 °C	—	14.80	19.74		
I_{DD_VLLS1}	Very-low-leakage stop mode 1 current • at 3.0 V				µA	
	• at 25°C	—	0.64	0.81		
	• at 50°C	—	1.14	1.50		
	• at 70°C	—	2.35	3.20		
	• at 85°C	—	4.37	5.80		
	• at 105°C	—	12.40	16.13		
I_{DD_VLLS0}	Very-low-leakage stop mode 0 current (SMC_STOPCTRL[PORPO] = 0) • at 3.0 V				µA	
	• at 25 °C	—	0.38	0.54		
	• at 50 °C	—	0.88	1.23		
	• at 70 °C	—	2.10	2.95		
	• at 85 °C	—	4.14	5.59		
	• at 105 °C	—	12.00	15.73		
I_{DD_VLLS0}	Very-low-leakage stop mode 0 current (SMC_STOPCTRL[PORPO] = 1) • at 3.0 V				µA	6
	• at 25 °C	—	0.30	0.45		
	• at 50 °C	—	0.79	1.12		
	• at 70 °C	—	2.01	2.82		
	• at 85 °C	—	4.05	5.45		
	• at 105 °C	—	11.96	15.63		

1. Data based on characterization results.

2. The analog supply current is the sum of the active or disabled current for each of the analog modules on the device. See each module's specification for its supply current.
3. MCG configured for FEI mode.
4. Incremental current consumption from peripheral activity is not included.
5. MCG configured for BLPI mode.
6. No brownout

Table 10. Low power mode peripheral adders — typical value

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
$I_{IREFSTEN4MHz}$	4 MHz internal reference clock (IRC) adder. Measured by entering STOP or VLPS mode with 4 MHz IRC enabled.	56	56	56	56	56	56	µA
$I_{IREFSTEN32KHz}$	32 kHz internal reference clock (IRC) adder. Measured by entering STOP mode with the 32 kHz IRC enabled.	52	52	52	52	52	52	µA
$I_{EREFSTEN4MHz}$	External 4 MHz crystal clock adder. Measured by entering STOP or VLPS mode with the crystal enabled.	206	228	237	245	251	258	uA
$I_{EREFSTEN32KHz}$	External 32 kHz crystal clock adder by means of the OSC0_CR[EREFSTEN and EREFSTEN] bits. Measured by entering all modes with the crystal enabled. • VLLS1 • VLLS3 • LLS • VLPS • STOP	 440 440 490 510 510	 490 490 490 560 560	 540 540 540 560 560	 560 560 560 560 560	 570 570 570 610 610	 580 580 680 680 680	nA
I_{CMP}	CMP peripheral adder measured by placing the device in VLLS1 mode with CMP enabled using the 6-bit DAC and a single external input for compare. Includes 6-bit DAC power consumption.	22	22	22	22	22	22	µA
I_{RTC}	RTC peripheral adder measured by placing the device in VLLS1 mode with external 32 kHz crystal enabled by means of the RTC_CR[OSCE] bit and the RTC ALARM set for 1 minute. Includes ERCLK32K (32 kHz external crystal) power consumption.	432	357	388	475	532	810	nA
I_{UART}	UART peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source waiting for RX data at 115200 baud rate. Includes selected clock source power consumption. • MCGIRCLK (4 MHz internal reference clock) • OSCERCLK (4 MHz external crystal)	 66 214	 66 237	 66 246	 66 254	 66 260	 66 268	µA

Table continues on the next page...

Table 10. Low power mode peripheral adders — typical value (continued)

Symbol	Description	Temperature (°C)						Unit
		-40	25	50	70	85	105	
I_{TPM}	TPM peripheral adder measured by placing the device in STOP or VLPS mode with selected clock source configured for output compare generating 100 Hz clock signal. No load is placed on the I/O generating the clock signal. Includes selected clock source and I/O switching currents. • MCGIRCLK (4 MHz internal reference clock) • OSCERCLK (4 MHz external crystal)	86 235	86 256	86 265	86 274	86 280	86 287	µA
I_{BG}	Bandgap adder when BGEN bit is set and device is placed in VLPx, LLS, or VLLSx mode.	45	45	45	45	45	45	µA
I_{ADC}	ADC peripheral adder combining the measured values at V_{DD} and V_{DDA} by placing the device in STOP or VLPS mode. ADC is configured for low power mode using the internal clock and continuous conversions.	366	366	366	366	366	366	µA

2.2.5.1 Diagram: Typical IDD_RUN operating behavior

The following data was measured under these conditions:

- MCG in FBE for run mode, and BLPE for VLPR mode
- No GPIOs toggled
- Code execution from flash with cache enabled
- For the ALLOFF curve, all peripheral clocks are disabled except FTFA

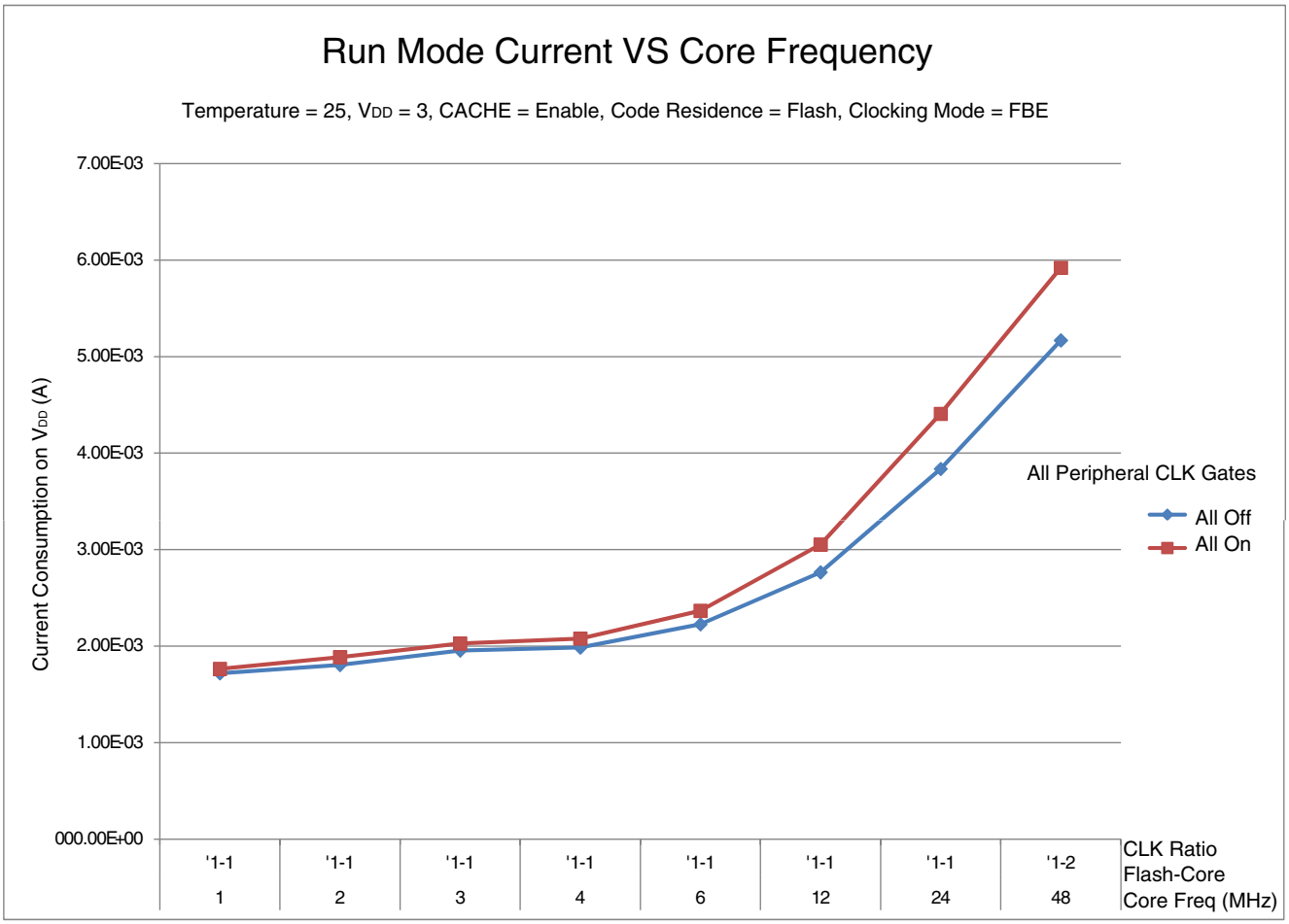


Figure 2. Run mode supply current vs. core frequency

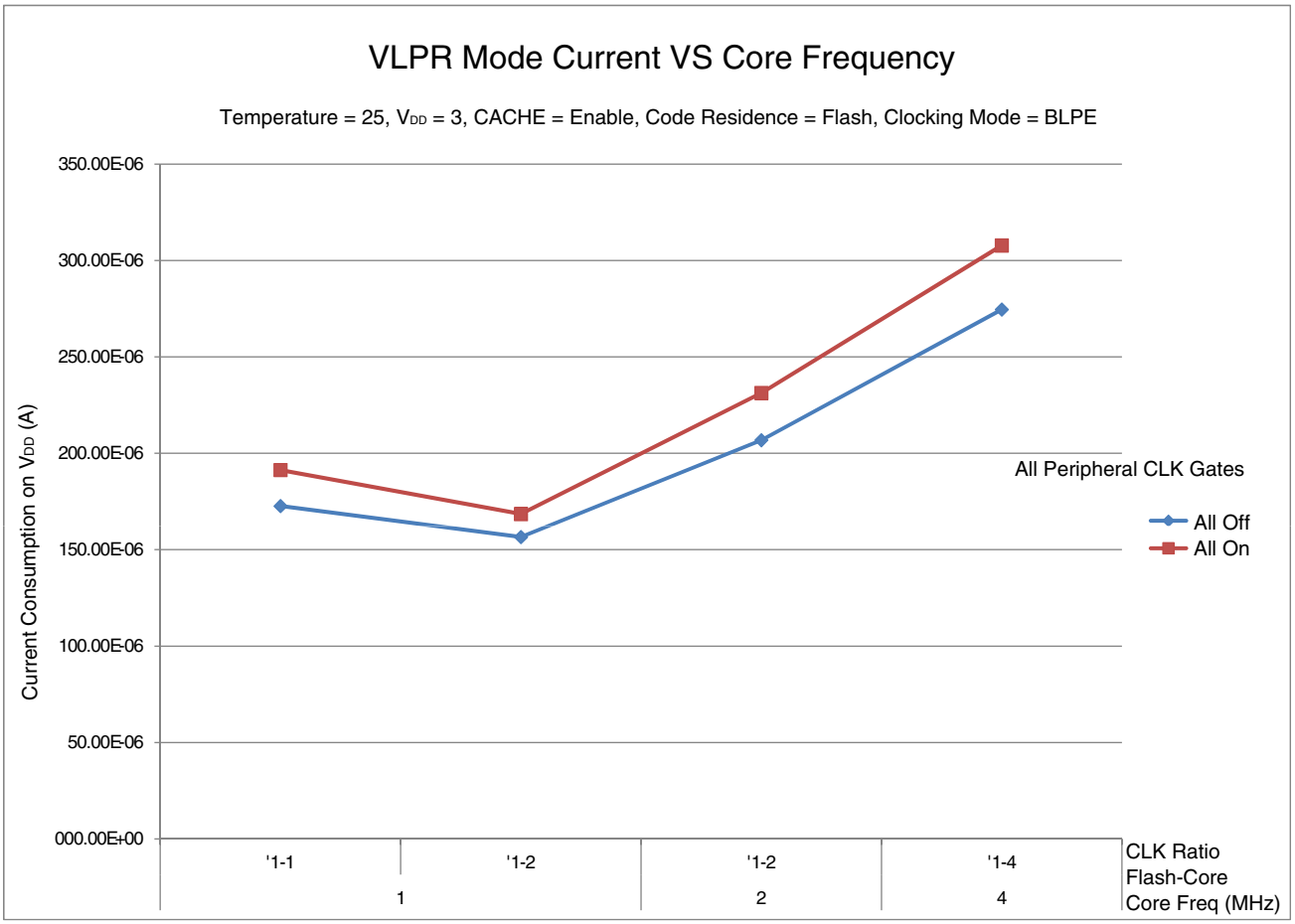


Figure 3. VLPR mode current vs. core frequency

2.2.6 EMC performance

Electromagnetic compatibility (EMC) performance is highly dependent on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation play a significant role in EMC performance. The system designer must consult the following Freescale applications notes, available on **freescale.com** for advice and guidance specifically targeted at optimizing EMC performance.

- AN2321: Designing for Board Level Electromagnetic Compatibility
- AN1050: Designing for Electromagnetic Compatibility (EMC) with HCMOS Microcontrollers
- AN1263: Designing for Electromagnetic Compatibility with Single-Chip Microcontrollers

- AN2764: Improving the Transient Immunity Performance of Microcontroller-Based Applications
- AN1259: System Design and Layout Techniques for Noise Reduction in MCU-Based Systems

2.2.7 Capacitance attributes

Table 11. Capacitance attributes

Symbol	Description	Min.	Max.	Unit
C_{IN}	Input capacitance	—	7	pF

2.3 Switching specifications

2.3.1 Device clock specifications

Table 12. Device clock specifications

Symbol	Description	Min.	Max.	Unit
Normal run mode				
f_{SYS}	System and core clock	—	48	MHz
f_{BUS}	Bus clock	—	24	MHz
f_{FLASH}	Flash clock	—	24	MHz
f_{LPTMR}	LPTMR clock	—	24	MHz
VLPR and VLPS modes[1]				
f_{SYS}	System and core clock	—	4	MHz
f_{BUS}	Bus clock	—	1	MHz
f_{FLASH}	Flash clock	—	1	MHz
f_{LPTMR}	LPTMR clock[2]	—	24	MHz
f_{ERCLK}	External reference clock	—	16	MHz
f_{LPTMR_ERCLK}	LPTMR external reference clock	—	16	MHz
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	—	16	MHz
f_{TPM}	TPM asynchronous clock	—	8	MHz
f_{UART0}	UART0 asynchronous clock	—	8	MHz

1. The frequency limitations in VLPR and VLPS modes here override any frequency specification listed in the timing specification for any other module. These same frequency limits apply to VLPS, whether VLPS was entered from RUN or from VLPR.
2. The LPTMR can be clocked at this speed in VLPR or VLPS only when the source is an external pin.

2.3.2 General switching specifications

These general-purpose specifications apply to all signals configured for GPIO and UART signals.

Table 13. General switching specifications

Description	Min.	Max.	Unit	Notes
GPIO pin interrupt pulse width (digital glitch filter disabled) — Synchronous path	1.5	—	Bus clock cycles	1
External RESET and NMI pin interrupt pulse width — Asynchronous path	100	—	ns	2
GPIO pin interrupt pulse width — Asynchronous path	16	—	ns	2
Port rise and fall time	—	36	ns	3

1. The greater synchronous and asynchronous timing must be met.
2. This is the shortest pulse that is guaranteed to be recognized.
3. 75 pF load

2.4 Thermal specifications

2.4.1 Thermal operating requirements

Table 14. Thermal operating requirements

Symbol	Description	Min.	Max.	Unit
T_J	Die junction temperature	–40	125	°C
T_A	Ambient temperature	–40	105	°C

2.4.2 Thermal attributes

Table 15. Thermal attributes

Board type	Symbol	Description	48 LQFP	32 LQFP	32 QFN	24 QFN	Unit	Notes
Single-layer (1S)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	82	88	97	110	°C/W	1
Four-layer (2s2p)	$R_{\theta JA}$	Thermal resistance, junction to ambient (natural convection)	58	59	34	42	°C/W	

Table continues on the next page...

Table 15. Thermal attributes (continued)

Board type	Symbol	Description	48 LQFP	32 LQFP	32 QFN	24 QFN	Unit	Notes
Single-layer (1S)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	70	74	81	92	°C/W	
Four-layer (2s2p)	$R_{\theta JMA}$	Thermal resistance, junction to ambient (200 ft./min. air speed)	52	52	28	36	°C/W	
—	$R_{\theta JB}$	Thermal resistance, junction to board	36	35	13	18	°C/W	2
—	$R_{\theta JC}$	Thermal resistance, junction to case	27	26	2.3	3.7	°C/W	3
—	Ψ_{JT}	Thermal characterization parameter, junction to package top outside center (natural convection)	8	8	8	10	°C/W	4

1. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*, or EIA/JEDEC Standard JESD51-6, *Integrated Circuit Thermal Test Method Environmental Conditions—Forced Convection (Moving Air)*.
2. Determined according to JEDEC Standard JESD51-8, *Integrated Circuit Thermal Test Method Environmental Conditions—Junction-to-Board*.
3. Determined according to Method 1012.1 of MIL-STD 883, *Test Method Standard, Microcircuits*, with the cold plate temperature used for the case temperature. The value includes the thermal resistance of the interface material between the top of the package and the cold plate.
4. Determined according to JEDEC Standard JESD51-2, *Integrated Circuits Thermal Test Method Environmental Conditions—Natural Convection (Still Air)*.

3 Peripheral operating requirements and behaviors

3.1 Core modules

3.1.1 SWD electricals

Table 16. SWD full voltage range electricals

Symbol	Description	Min.	Max.	Unit
	Operating voltage	1.71	3.6	V
J1	SWD_CLK frequency of operation • Serial wire debug	0	25	MHz
J2	SWD_CLK cycle period	1/J1	—	ns
J3	SWD_CLK clock pulse width			

Table continues on the next page...

Table 16. SWD full voltage range electricals (continued)

Symbol	Description	Min.	Max.	Unit
	• Serial wire debug	20	—	ns
J4	SWD_CLK rise and fall times	—	3	ns
J9	SWD_DIO input data setup time to SWD_CLK rise	10	—	ns
J10	SWD_DIO input data hold time after SWD_CLK rise	0	—	ns
J11	SWD_CLK high to SWD_DIO data valid	—	32	ns
J12	SWD_CLK high to SWD_DIO high-Z	5	—	ns

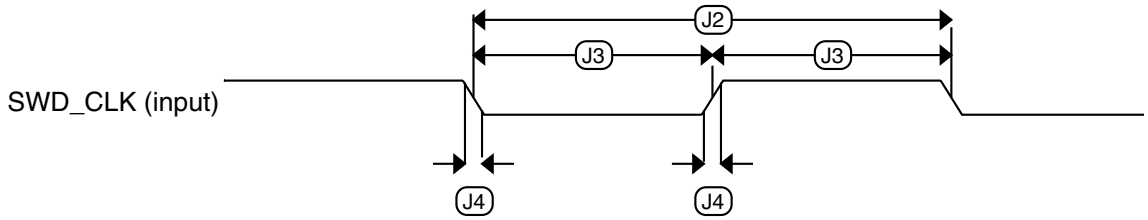


Figure 4. Serial wire clock input timing

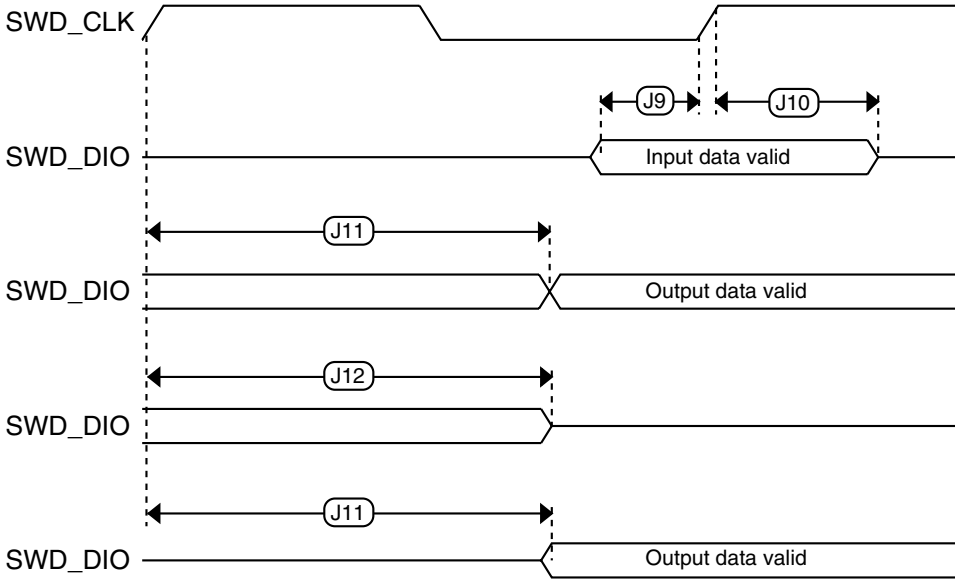


Figure 5. Serial wire data timing

3.2 System modules

There are no specifications necessary for the device's system modules.

3.3 Clock modules

3.3.1 MCG specifications

Table 17. MCG specifications

Symbol	Description		Min.	Typ.	Max.	Unit	Notes
f_{ints_ft}	Internal reference frequency (slow clock) — factory trimmed at nominal V_{DD} and 25 °C		—	32.768	—	kHz	
f_{ints_t}	Internal reference frequency (slow clock) — user trimmed		31.25	—	39.0625	kHz	
$\Delta_{fdco\_res\_t}$	Resolution of trimmed average DCO output frequency at fixed voltage and temperature — using C3[SCTRIM] and C4[SCFTRIM]		—	± 0.3	± 0.6	$\%f_{dco}$	1
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over voltage and temperature		—	+0.5/-0.7	± 3	$\%f_{dco}$	1, 2
Δf_{dco_t}	Total deviation of trimmed average DCO output frequency over fixed voltage and temperature range of 0–70 °C		—	± 0.4	± 1.5	$\%f_{dco}$	1, 2
f_{intf_ft}	Internal reference frequency (fast clock) — factory trimmed at nominal V_{DD} and 25 °C		—	4	—	MHz	
Δf_{intf_ft}	Frequency deviation of internal reference clock (fast clock) over temperature and voltage — factory trimmed at nominal V_{DD} and 25 °C		—	+1/-2	± 3	$\%f_{intf\_ft}$	2
f_{intf_t}	Internal reference frequency (fast clock) — user trimmed at nominal V_{DD} and 25 °C		3	—	5	MHz	
f_{loc_low}	Loss of external clock minimum frequency — RANGE = 00		(3/5) x f_{ints_t}	—	—	kHz	
f_{loc_high}	Loss of external clock minimum frequency — RANGE = 01, 10, or 11		(16/5) x f_{ints_t}	—	—	kHz	
FLL							
f_{fll_ref}	FLL reference frequency range		31.25	—	39.0625	kHz	
f_{dco}	DCO output frequency range	Low range (DRS = 00) 640 × f_{fll_ref}	20	20.97	25	MHz	3, 4
		Mid range (DRS = 01) 1280 × f_{fll_ref}	40	41.94	48	MHz	
$f_{dco\_t\_DMX32}$	DCO output frequency	Low range (DRS = 00) 732 × f_{fll_ref}	—	23.99	—	MHz	5, 6
		Mid range (DRS = 01)	—	47.97	—	MHz	

Table continues on the next page...

Table 17. MCG specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	1464 × f_{fll_ref}					
J_{cyc_fll}	FLL period jitter • f_{VCO} = 48 MHz	—	180	—	ps	7
$t_{fll\_acquire}$	FLL target frequency acquisition time	—	—	1	ms	8

1. This parameter is measured with the internal reference (slow clock) being used as a reference to the FLL (FEI clock mode).
2. The deviation is relative to the factory trimmed frequency at nominal V_{DD} and 25 °C, f_{ints_ft}.
3. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 0.
4. The resulting system clock frequencies must not exceed their maximum specified values. The DCO frequency deviation (Δf_{dco_t}) over voltage and temperature must be considered.
5. These typical values listed are with the slow internal reference clock (FEI) using factory trim and DMX32 = 1.
6. The resulting clock frequency must not exceed the maximum specified clock frequency of the device.
7. This specification is based on standard deviation (RMS) of period or frequency.
8. This specification applies to any time the FLL reference source or reference divider is changed, trim value is changed, DMX32 bit is changed, DRS bits are changed, or changing from FLL disabled (BLPE, BLPI) to FLL enabled (FEI, FEE, FBE, FBI). If a crystal/resonator is being used as the reference, this specification assumes it is already running.

3.3.2 Oscillator electrical specifications

3.3.2.1 Oscillator DC electrical specifications

Table 18. Oscillator DC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
V_{DD}	Supply voltage	1.71	—	3.6	V	
I_{DDOSC}	Supply current — low-power mode (HGO=0)					1
	• 32 kHz	—	500	—	nA	
	• 4 MHz	—	200	—	µA	
	• 8 MHz (RANGE=01)	—	300	—	µA	
	• 16 MHz	—	950	—	µA	
	• 24 MHz	—	1.2	—	mA	
	• 32 MHz	—	1.5	—	mA	
I_{DDOSC}	Supply current — high gain mode (HGO=1)					1
	• 32 kHz	—	25	—	µA	
	• 4 MHz	—	400	—	µA	
	• 8 MHz (RANGE=01)	—	500	—	µA	
	• 16 MHz	—	2.5	—	mA	
		—	3	—	mA	
		—	4	—	mA	

Table continues on the next page...

Table 18. Oscillator DC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
	• 24 MHz • 32 MHz					
C_x	EXTAL load capacitance	—	—	—		2, 3
C_y	XTAL load capacitance	—	—	—		2, 3
R_F	Feedback resistor — low-frequency, low-power mode (HGO=0)	—	—	—	MΩ	2, 4
	Feedback resistor — low-frequency, high-gain mode (HGO=1)	—	10	—	MΩ	
	Feedback resistor — high-frequency, low-power mode (HGO=0)	—	—	—	MΩ	
	Feedback resistor — high-frequency, high-gain mode (HGO=1)	—	1	—	MΩ	
R_S	Series resistor — low-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — low-frequency, high-gain mode (HGO=1)	—	200	—	kΩ	
	Series resistor — high-frequency, low-power mode (HGO=0)	—	—	—	kΩ	
	Series resistor — high-frequency, high-gain mode (HGO=1)	—	0	—	kΩ	
V_{pp}[5]	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — low-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, low-power mode (HGO=0)	—	0.6	—	V	
	Peak-to-peak amplitude of oscillation (oscillator mode) — high-frequency, high-gain mode (HGO=1)	—	V_{DD}	—	V	

1. V_{DD}=3.3 V, Temperature =25 °C
2. See crystal or resonator manufacturer's recommendation
3. C_x,C_y can be provided by using the integrated capacitors when the low frequency oscillator (RANGE = 00) is used. For all other cases external capacitors must be used.
4. When low power mode is selected, R_F is integrated and must not be attached externally.
5. The EXTAL and XTAL pins should only be connected to required oscillator components and must not be connected to any other devices.

3.3.2.2 Oscillator frequency specifications

Table 19. Oscillator frequency specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
f_{osc_lo}	Oscillator crystal or resonator frequency — low-frequency mode (MCG_C2[RANGE]=00)	32	—	40	kHz	
$f_{osc\_hi\_1}$	Oscillator crystal or resonator frequency — high-frequency mode (low range) (MCG_C2[RANGE]=01)	3	—	8	MHz	
$f_{osc\_hi\_2}$	Oscillator crystal or resonator frequency — high frequency mode (high range) (MCG_C2[RANGE]=1x)	8	—	32	MHz	
f_{ec_extal}	Input clock frequency (external clock mode)	—	—	48	MHz	1, 2
t_{dc_extal}	Input clock duty cycle (external clock mode)	40	50	60	%	
t_{cst}	Crystal startup time — 32 kHz low-frequency, low-power mode (HGO=0)	—		—	ms	3, 4
	Crystal startup time — 32 kHz low-frequency, high-gain mode (HGO=1)	—		—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), low-power mode (HGO=0)	—	0.6	—	ms	
	Crystal startup time — 8 MHz high-frequency (MCG_C2[RANGE]=01), high-gain mode (HGO=1)	—	1	—	ms	

1. Other frequency limits may apply when external clock is being used as a reference for the FLL
2. When transitioning from FEI or FBI to FBE mode, restrict the frequency of the input clock so that, when it is divided by FRDIV, it remains within the limits of the DCO input clock frequency.
3. Proper PC board layout procedures must be followed to achieve specifications.
4. Crystal startup time is defined as the time between the oscillator being enabled and the OSCINIT bit in the MCG_S register being set.

3.4 Memories and memory interfaces

3.4.1 Flash electrical specifications

This section describes the electrical characteristics of the flash memory module.

3.4.1.1 Flash timing specifications — program and erase

The following specifications represent the amount of time the internal charge pumps are active and do not include command overhead.

Table 20. NVM program/erase timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
t_{hvpgm4}	Longword Program high-voltage time	—	7.5	18	µs	
$t_{hversscr}$	Sector Erase high-voltage time	—	13	113	ms	1
$t_{hversall}$	Erase All high-voltage time	—	52	452	ms	1

1. Maximum time based on expectations at cycling end-of-life.

3.4.1.2 Flash timing specifications — commands

Table 21. Flash command timing specifications

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{rd1sec1k}$	Read 1s Section execution time (flash sector)	—	—	60	µs	1
t_{pgmchk}	Program Check execution time	—	—	45	µs	1
t_{rdrsrc}	Read Resource execution time	—	—	30	µs	1
t_{pgm4}	Program Longword execution time	—	65	145	µs	
t_{ersscr}	Erase Flash Sector execution time	—	14	114	ms	2
t_{rd1all}	Read 1s All Blocks execution time	—	—	0.5	ms	
t_{rdonce}	Read Once execution time	—	—	25	µs	1
$t_{pgmonce}$	Program Once execution time	—	65	—	µs	
t_{ersall}	Erase All Blocks execution time	—	61	500	ms	2
t_{vfykey}	Verify Backdoor Access Key execution time	—	—	30	µs	1

1. Assumes 25 MHz flash clock frequency.
2. Maximum times for erase parameters based on expectations at cycling end-of-life.

3.4.1.3 Flash high voltage current behaviors

Table 22. Flash high voltage current behaviors

Symbol	Description	Min.	Typ.	Max.	Unit
I_{DD_PGM}	Average current adder during high voltage flash programming operation	—	2.5	6.0	mA
I_{DD_ERS}	Average current adder during high voltage flash erase operation	—	1.5	4.0	mA

3.4.1.4 Reliability specifications

Table 23. NVM reliability specifications

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
Program Flash						

Table continues on the next page...

Table 23. NVM reliability specifications (continued)

Symbol	Description	Min.	Typ.[1]	Max.	Unit	Notes
$t_{nvmretp10k}$	Data retention after up to 10 K cycles	5	50	—	years	
$t_{nvmretp1k}$	Data retention after up to 1 K cycles	20	100	—	years	
$n_{nvmcycp}$	Cycling endurance	10 K	50 K	—	cycles	2

1. Typical data retention values are based on measured response accelerated at high temperature and derated to a constant 25 °C use profile. Engineering Bulletin EB618 does not apply to this technology. Typical endurance defined in Engineering Bulletin EB619.
2. Cycling endurance represents number of program/erase cycles at -40 °C ≤ T_j ≤ 125 °C.

3.5 Security and integrity modules

There are no specifications necessary for the device's security and integrity modules.

3.6 Analog

3.6.1 ADC electrical specifications

All ADC channels meet the 12-bit single-ended accuracy specifications.

3.6.1.1 12-bit ADC operating conditions

Table 24. 12-bit ADC operating conditions

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
V_{DDA}	Supply voltage	Absolute	1.71	—	3.6	V	
ΔV_{DDA}	Supply voltage	Delta to V_{DD} (V_{DD} – V_{DDA})	-100	0	+100	mV	2
ΔV_{SSA}	Ground voltage	Delta to V_{SS} (V_{SS} – V_{SSA})	-100	0	+100	mV	2
V_{REFH}	ADC reference voltage high		1.13	V_{DDA}	V_{DDA}	V	3
V_{REFL}	ADC reference voltage low		V_{SSA}	V_{SSA}	V_{SSA}	V	3
V_{ADIN}	Input voltage		V_{REFL}	—	V_{REFH}	V	
C_{ADIN}	Input capacitance	• 8-bit / 10-bit / 12-bit modes	—	4	5	pF	
R_{ADIN}	Input series resistance		—	2	5	kΩ	

Table continues on the next page...

Table 24. 12-bit ADC operating conditions (continued)

Symbol	Description	Conditions	Min.	Typ.[1]	Max.	Unit	Notes
R_{AS}	Analog source resistance (external)	12-bit modes f_{ADCK} < 4 MHz	—	—	5	kΩ	4
f_{ADCK}	ADC conversion clock frequency	≤ 12-bit mode	1.0	—	18.0	MHz	5
C_{rate}	ADC conversion rate	≤ 12-bit modes No ADC hardware averaging Continuous conversions enabled, subsequent conversion time	20.000	—	818.330	Ksps	6

1. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 1.0 MHz, unless otherwise stated. Typical values are for reference only, and are not tested in production.
2. DC potential difference.
3. For packages without dedicated VREFH and VREFL pins, V_{REFH} is internally tied to V_{DDA}, and V_{REFL} is internally tied to V_{SSA}.
4. This resistance is external to MCU. To achieve the best results, the analog source resistance must be kept as low as possible. The results in this data sheet were derived from a system that had < 8 Ω analog source resistance. The R_{AS}/C_{AS} time constant should be kept to < 1 ns.
5. To use the maximum ADC conversion clock frequency, CFG2[ADHSC] must be set and CFG1[ADLPC] must be clear.
6. For guidelines and examples of conversion rate calculation, download the ADC calculator tool.

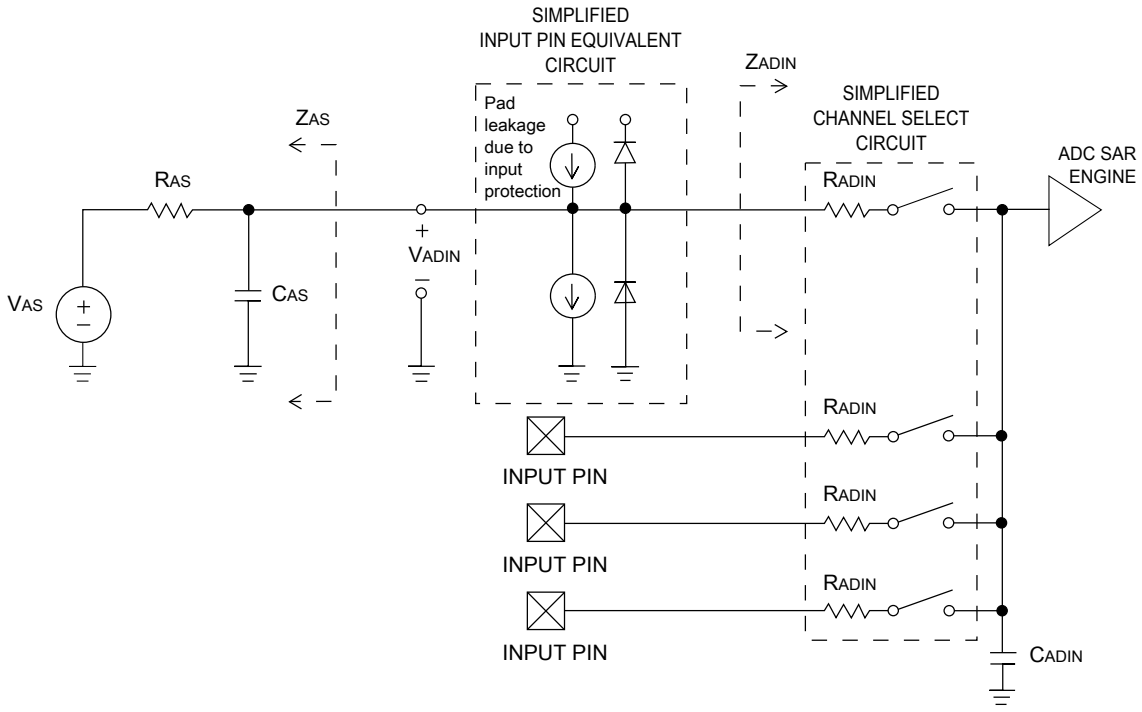


Figure 6. ADC input impedance equivalency diagram

3.6.1.2 12-bit ADC electrical characteristics

Table 25. 12-bit ADC characteristics ($V_{REFH} = V_{DDA}$, $V_{REFL} = V_{SSA}$)

Symbol	Description	Conditions[1]	Min.	Typ.[2]	Max.	Unit	Notes
I_{DDA_ADC}	Supply current		0.215	—	1.7	mA	3
f_{ADACK}	ADC asynchronous clock source	• ADLPC = 1, ADHSC = 0 • ADLPC = 1, ADHSC = 1 • ADLPC = 0, ADHSC = 0 • ADLPC = 0, ADHSC = 1	1.2 2.4 3.0 4.4	2.4 4.0 5.2 6.2	3.9 6.1 7.3 9.5	MHz MHz MHz MHz	$t_{ADACK} = 1/f_{ADACK}$
	Sample Time	See Reference Manual chapter for sample times					
TUE	Total unadjusted error	• 12-bit modes • <12-bit modes	— —	±4 ±1.4	±6.8 ±2.1	LSB[4]	5
DNL	Differential non-linearity	• 12-bit modes • <12-bit modes	— —	±0.7 ±0.2	–1.1 to +1.9 –0.3 to 0.5	LSB[4]	5
INL	Integral non-linearity	• 12-bit modes • <12-bit modes	— —	±1.0 ±0.5	–2.7 to +1.9 –0.7 to +0.5	LSB[4]	5
E_{FS}	Full-scale error	• 12-bit modes • <12-bit modes	— —	–4 –1.4	–5.4 –1.8	LSB[4]	$V_{ADIN} = V_{DDA}$[5]
E_Q	Quantization error	• 12-bit modes	—	—	±0.5	LSB[4]	
E_{IL}	Input leakage error		$I_{In} \times R_{AS}$			mV	I_{In} = leakage current (refer to the MCU's voltage and current operating ratings)
	Temp sensor slope	Across the full temperature range of the device	1.55	1.62	1.69	mV/°C	6
V_{TEMP25}	Temp sensor voltage	25 °C	706	716	726	mV	6

1. All accuracy numbers assume the ADC is calibrated with $V_{REFH} = V_{DDA}$
2. Typical values assume V_{DDA} = 3.0 V, Temp = 25 °C, f_{ADCK} = 2.0 MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

3. The ADC supply current depends on the ADC conversion clock speed, conversion rate and ADC_CFG1[ADLPC] (low power). For lowest power operation, ADC_CFG1[ADLPC] must be set, the ADC_CFG2[ADHSC] bit must be clear with 1 MHz ADC conversion clock speed.
4. 1 LSB = $(V_{REFH} - V_{REFL})/2^N$
5. ADC conversion clock < 16 MHz, Max hardware averaging (AVGE = %1, AVGS = %11)
6. ADC conversion clock < 3 MHz

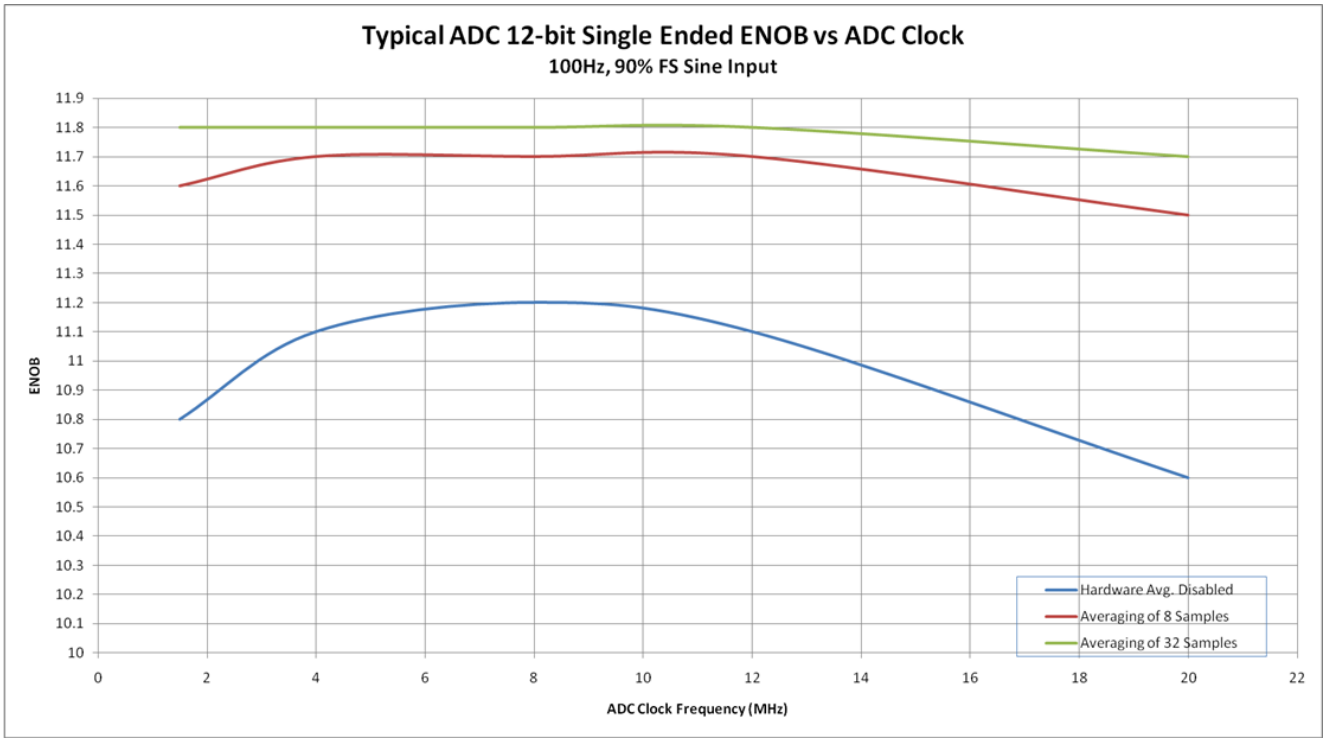


Figure 7. Typical ENOB vs. ADC_CLK for 12-bit single-ended mode

3.6.2 CMP and 6-bit DAC electrical specifications

Table 26. Comparator and 6-bit DAC electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
V_{DD}	Supply voltage	1.71	—	3.6	V
I_{DDHS}	Supply current, high-speed mode (EN = 1, PMODE = 1)	—	—	200	µA
I_{DDLS}	Supply current, low-speed mode (EN = 1, PMODE = 0)	—	—	20	µA
V_{AIN}	Analog input voltage	V_{SS}	—	V_{DD}	V
V_{AIO}	Analog input offset voltage	—	—	20	mV
V_H	Analog comparator hysteresis[1]				
	• CR0[HYSTCTR] = 00	—	5	—	mV
	• CR0[HYSTCTR] = 01	—	10	—	mV

Table continues on the next page...

Table 26. Comparator and 6-bit DAC electrical specifications (continued)

Symbol	Description	Min.	Typ.	Max.	Unit
	• CR0[HYSTCTR] = 10	—	20	—	mV
	• CR0[HYSTCTR] = 11	—	30	—	mV
V_{CMPOh}	Output high	V_{DD} – 0.5	—	—	V
V_{CMPOl}	Output low	—	—	0.5	V
t_{DHS}	Propagation delay, high-speed mode (EN = 1, PMODE = 1)	20	50	200	ns
t_{DLS}	Propagation delay, low-speed mode (EN = 1, PMODE = 0)	80	250	600	ns
	Analog comparator initialization delay[2]	—	—	40	µs
I_{DAC6b}	6-bit DAC current adder (enabled)	—	7	—	µA
INL	6-bit DAC integral non-linearity	–0.5	—	0.5	LSB[3]
DNL	6-bit DAC differential non-linearity	–0.3	—	0.3	LSB

1. Typical hysteresis is measured with input voltage range limited to 0.7 to V_{DD} – 0.7 V.
2. Comparator initialization delay is defined as the time between software writes to change control inputs (writes to DACEN, VRSEL, PSEL, MSEL, VOSEL) and the comparator output settling to a stable level.
3. 1 LSB = $V_{reference}$/64

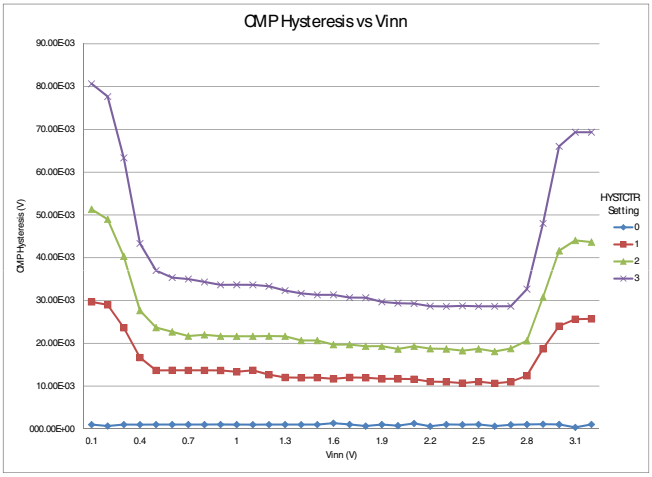


Figure 8. Typical hysteresis vs. Vin level (V_{DD} = 3.3 V, PMODE = 0)

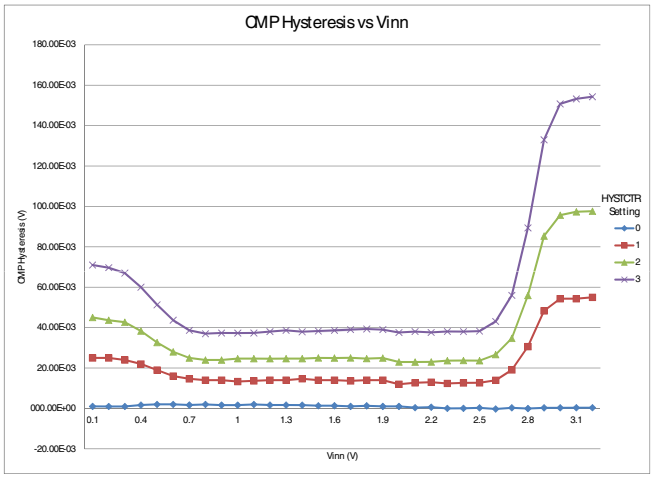


Figure 9. Typical hysteresis vs. Vin level (V_{DD} = 3.3 V, PMODE = 1)

3.6.3 12-bit DAC electrical characteristics

3.6.3.1 12-bit DAC operating requirements

Table 27. 12-bit DAC operating requirements

Symbol	Desciption	Min.	Max.	Unit	Notes
V_{DDA}	Supply voltage		3.6	V	
V_{DACR}	Reference voltage	1.13	3.6	V	1
C_L	Output load capacitance	—	100	pF	2
I_L	Output load current	—	1	mA	

1. The DAC reference can be selected to be V_{DDA} or V_{REFH}.
2. A small load capacitance (47 pF) can improve the bandwidth performance of the DAC.

3.6.3.2 12-bit DAC operating behaviors

Table 28. 12-bit DAC operating behaviors

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
I_{DDA_DACLP}	Supply current — low-power mode	—	—	250	µA	
I_{DDA_DACHP}	Supply current — high-speed mode	—	—	900	µA	
t_{DACLP}	Full-scale settling time (0x080 to 0xF7F) — low-power mode	—	100	200	µs	1
t_{DACHP}	Full-scale settling time (0x080 to 0xF7F) — high-power mode	—	15	30	µs	1

Table continues on the next page...

Table 28. 12-bit DAC operating behaviors (continued)

Symbol	Description	Min.	Typ.	Max.	Unit	Notes
$t_{CCDACLP}$	Code-to-code settling time (0xBF8 to 0xC08) — low-power mode and high-speed mode	—	0.7	1	µs	1
$V_{dacoutl}$	DAC output voltage range low — high-speed mode, no load, DAC set to 0x000	—	—	100	mV	
$V_{dacouth}$	DAC output voltage range high — high-speed mode, no load, DAC set to 0xFFF	V_{DACR} −100	—	V_{DACR}	mV	
INL	Integral non-linearity error — high speed mode	—	—	±8	LSB	2
DNL	Differential non-linearity error — V_{DACR} > 2 V	—	—	±1	LSB	3
DNL	Differential non-linearity error — V_{DACR} = VREF_OUT	—	—	±1	LSB	4
V_{OFFSET}	Offset error	—	±0.4	±0.8	%FSR	5
E_G	Gain error	—	±0.1	±0.6	%FSR	5
PSRR	Power supply rejection ratio, V_{DDA} ≥ 2.4 V	60	—	90	dB	
T_{CO}	Temperature coefficient offset voltage	—	3.7	—	µV/C	6
T_{GE}	Temperature coefficient gain error	—	0.000421	—	%FSR/C	
Rop	Output resistance (load = 3 kΩ)	—	—	250	Ω	
SR	Slew rate -80h→ F7Fh→ 80h				V/µs	
	• High power (SP_{HP})	1.2	1.7	—		
	• Low power (SP_{LP})	0.05	0.12	—		
BW	3dB bandwidth				kHz	
	• High power (SP_{HP})	550	—	—		
	• Low power (SP_{LP})	40	—	—		

1. Settling within ±1 LSB
2. The INL is measured for 0 + 100 mV to V_{DACR} −100 mV
3. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV
4. The DNL is measured for 0 + 100 mV to V_{DACR} −100 mV with V_{DDA} > 2.4 V
5. Calculated by a best fit curve from V_{SS} + 100 mV to V_{DACR} − 100 mV
6. V_{DDA} = 3.0 V, reference select set for V_{DDA} (DACx_CO:DACRFS = 1), high power mode (DACx_C0:LPEN = 0), DAC set to 0x800, temperature range is across the full range of the device

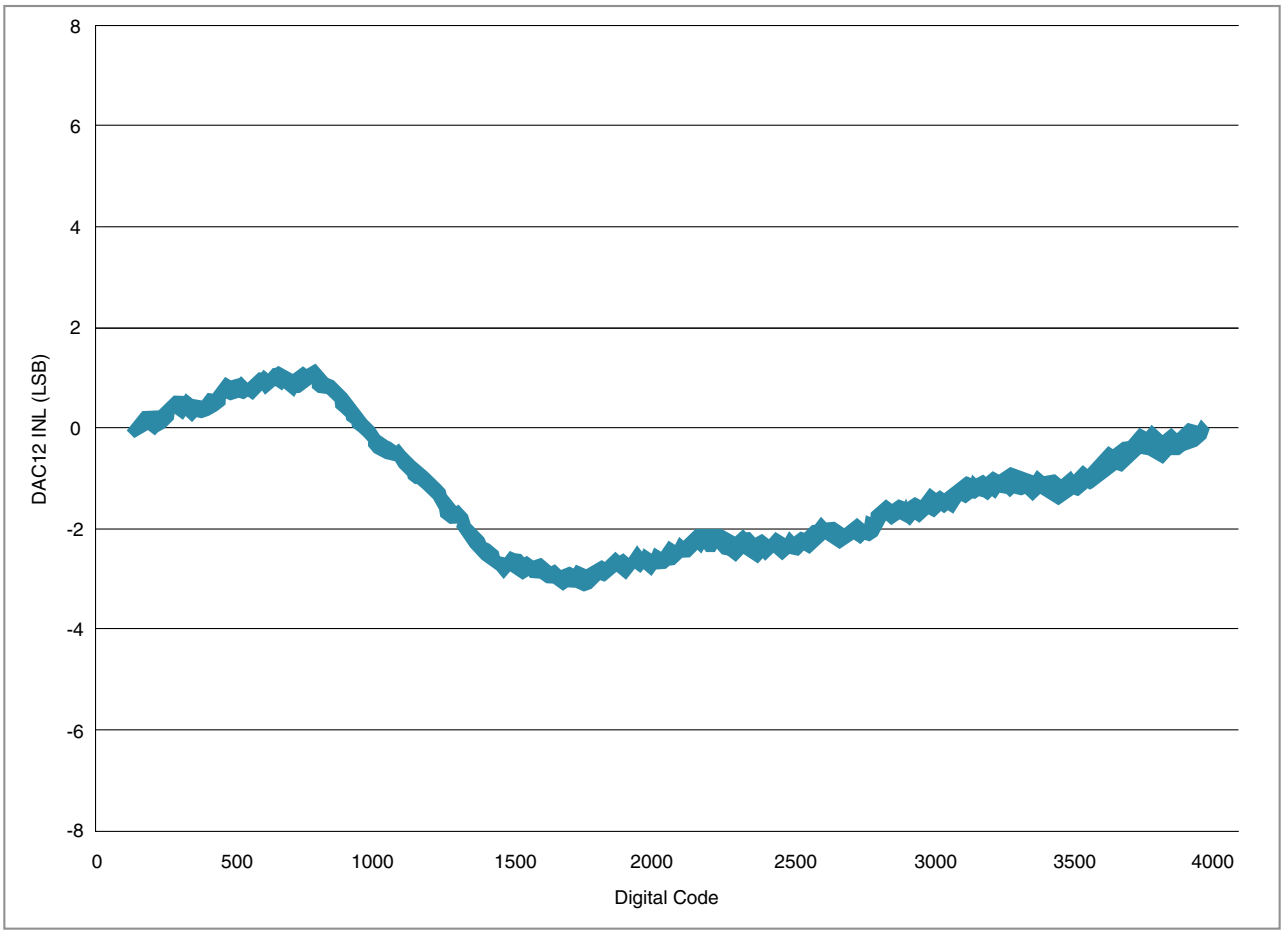


Figure 10. Typical INL error vs. digital code

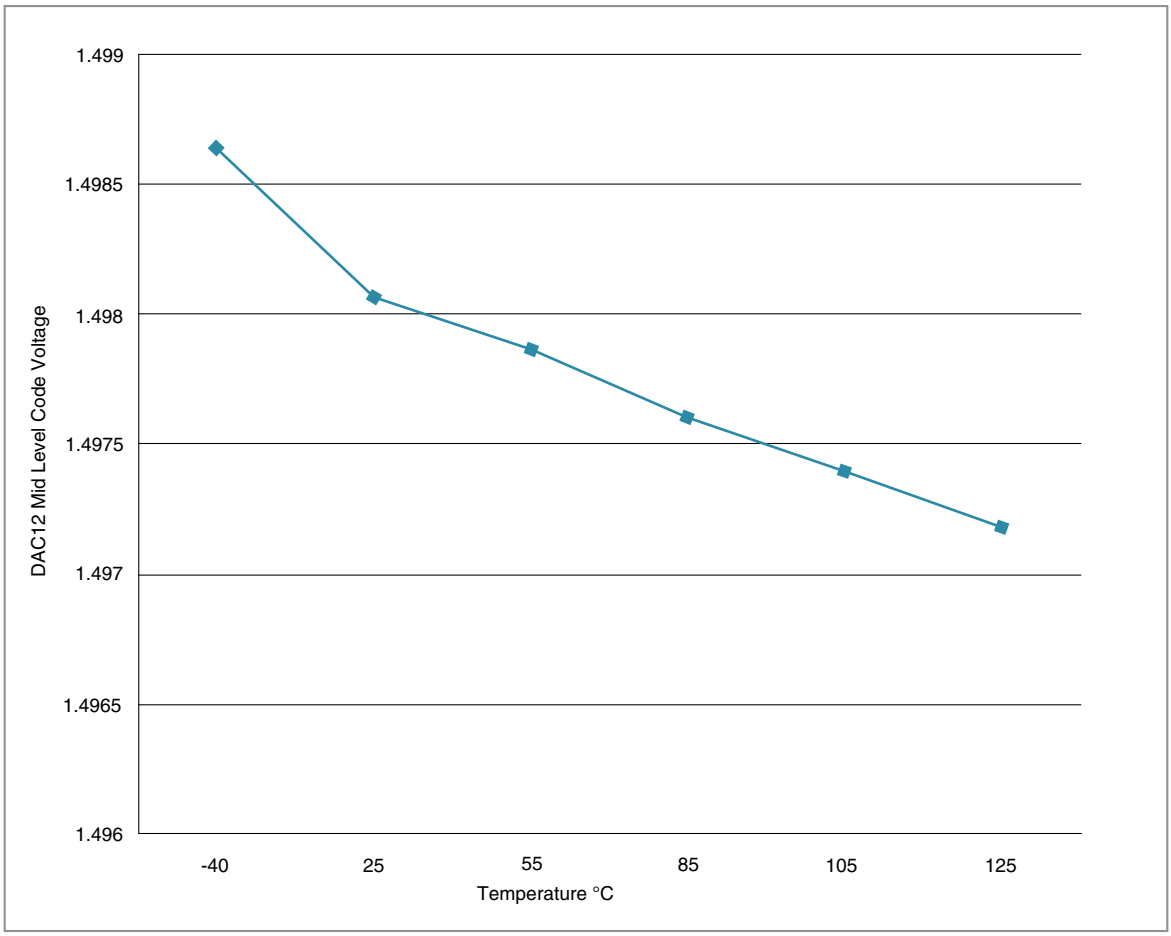


Figure 11. Offset at half scale vs. temperature

3.7 Timers

See General switching specifications.

3.8 Communication interfaces

3.8.1 SPI switching specifications

The Serial Peripheral Interface (SPI) provides a synchronous serial bus with master and slave operations. Many of the transfer attributes are programmable. The following tables provide timing characteristics for classic SPI timing modes. See the SPI chapter of the chip's Reference Manual for information about the modified transfer formats used for communicating with slower peripheral devices.

All timing is shown with respect to 20% V_{DD} and 80% V_{DD} thresholds, unless noted, as well as input signal transitions of 3 ns and a 30 pF maximum load on all SPI pins.

Table 29. SPI master mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	2 x t_{periph}	2048 x t_{periph}	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} – 30	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	16	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—
8	t_{v}	Data valid (after SPSCK edge)	—	10	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	t_{periph} – 25	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0, f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$

Table 30. SPI master mode timing on slew rate enabled pads

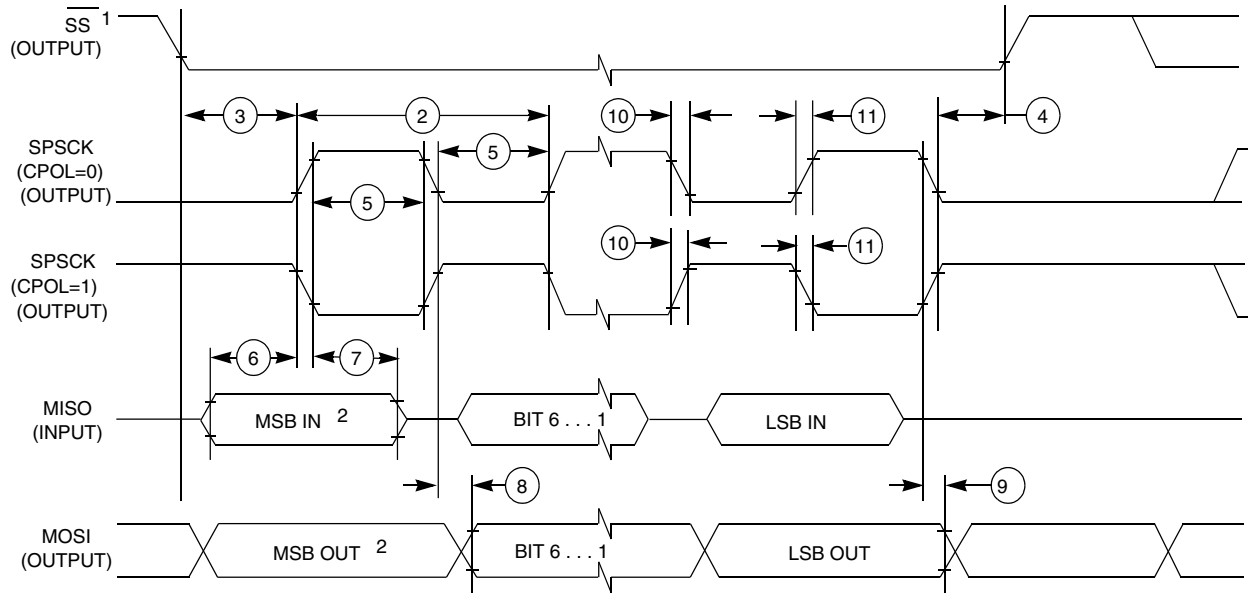
Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	$f_{periph}/2048$	$f_{periph}/2$	Hz	1
2	t_{SPSCK}	SPSCK period	2 x t_{periph}	2048 x t_{periph}	ns	2
3	t_{Lead}	Enable lead time	1/2	—	t_{SPSCK}	—
4	t_{Lag}	Enable lag time	1/2	—	t_{SPSCK}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} – 30	1024 x t_{periph}	ns	—
6	t_{SU}	Data setup time (inputs)	96	—	ns	—
7	t_{HI}	Data hold time (inputs)	0	—	ns	—

Table continues on the next page...

Table 30. SPI master mode timing on slew rate enabled pads (continued)

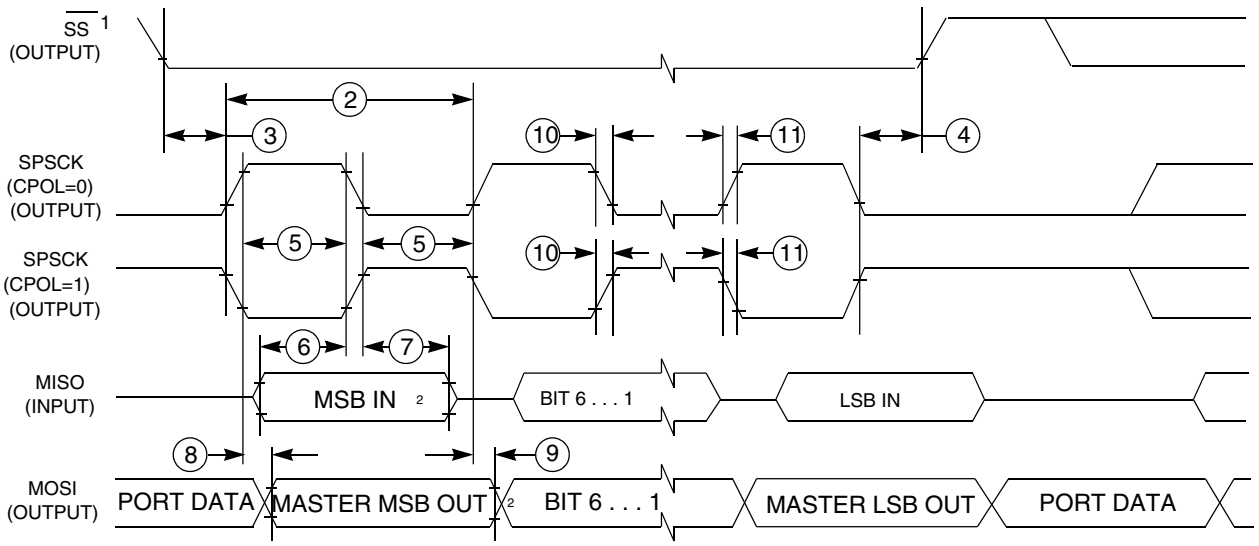
Num.	Symbol	Description	Min.	Max.	Unit	Note
8	t_v	Data valid (after SPSCK edge)	—	52	ns	—
9	t_{HO}	Data hold time (outputs)	0	—	ns	—
10	t_{RI}	Rise time input	—	$t_{periph} - 25$	ns	—
	t_{FI}	Fall time input				
11	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0, f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$



1. If configured as an output.
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 12. SPI master mode timing (CPHA = 0)



1.If configured as output

2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 13. SPI master mode timing (CPHA = 1)

Table 31. SPI slave mode timing on slew rate disabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCK}	SPSCK period	4 x t_{periph}	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} – 30	—	ns	—
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCK edge)	—	22	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{periph} – 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	25	ns	—
	t_{FO}	Fall time output				

1. For SPI0, f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

Table 32. SPI slave mode timing on slew rate enabled pads

Num.	Symbol	Description	Min.	Max.	Unit	Note
1	f_{op}	Frequency of operation	0	$f_{periph}/4$	Hz	1
2	t_{SPSCK}	SPSCK period	4 x t_{periph}	—	ns	2
3	t_{Lead}	Enable lead time	1	—	t_{periph}	—
4	t_{Lag}	Enable lag time	1	—	t_{periph}	—
5	t_{WSPSCK}	Clock (SPSCK) high or low time	t_{periph} – 30	—	ns	—
6	t_{SU}	Data setup time (inputs)	2	—	ns	—
7	t_{HI}	Data hold time (inputs)	7	—	ns	—
8	t_a	Slave access time	—	t_{periph}	ns	3
9	t_{dis}	Slave MISO disable time	—	t_{periph}	ns	4
10	t_v	Data valid (after SPSCK edge)	—	122	ns	—
11	t_{HO}	Data hold time (outputs)	0	—	ns	—
12	t_{RI}	Rise time input	—	t_{periph} – 25	ns	—
	t_{FI}	Fall time input				
13	t_{RO}	Rise time output	—	36	ns	—
	t_{FO}	Fall time output				

1. For SPI0, f_{periph} is the bus clock (f_{BUS}).
2. $t_{periph} = 1/f_{periph}$
3. Time to data active from high-impedance state
4. Hold time to high-impedance state

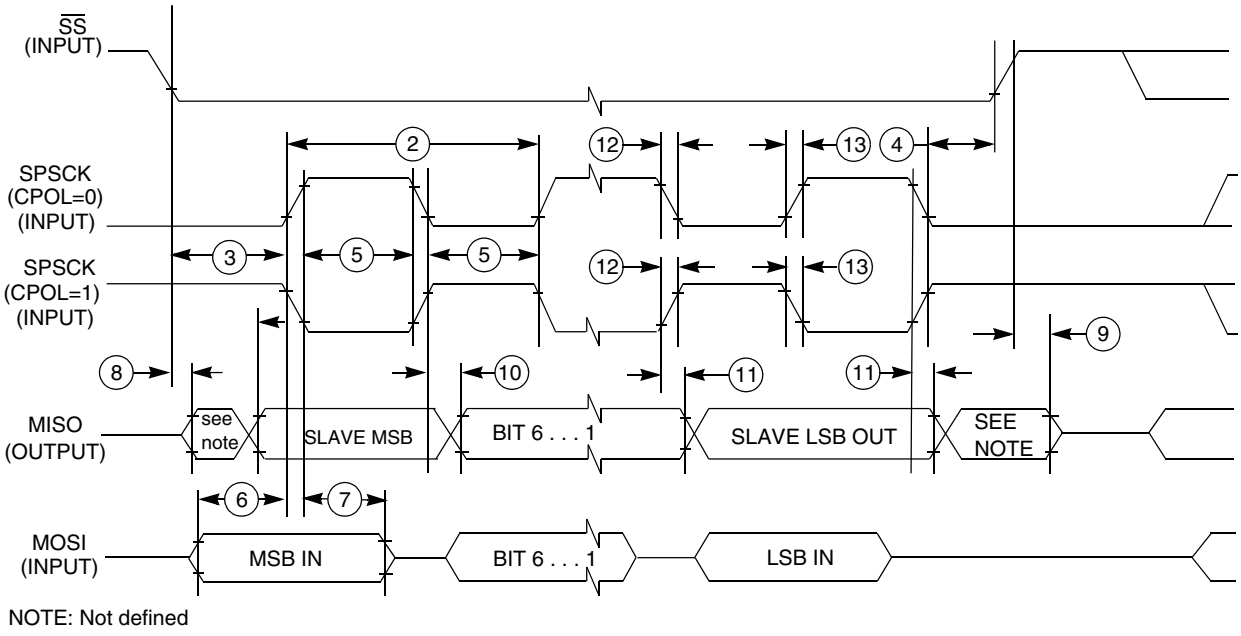
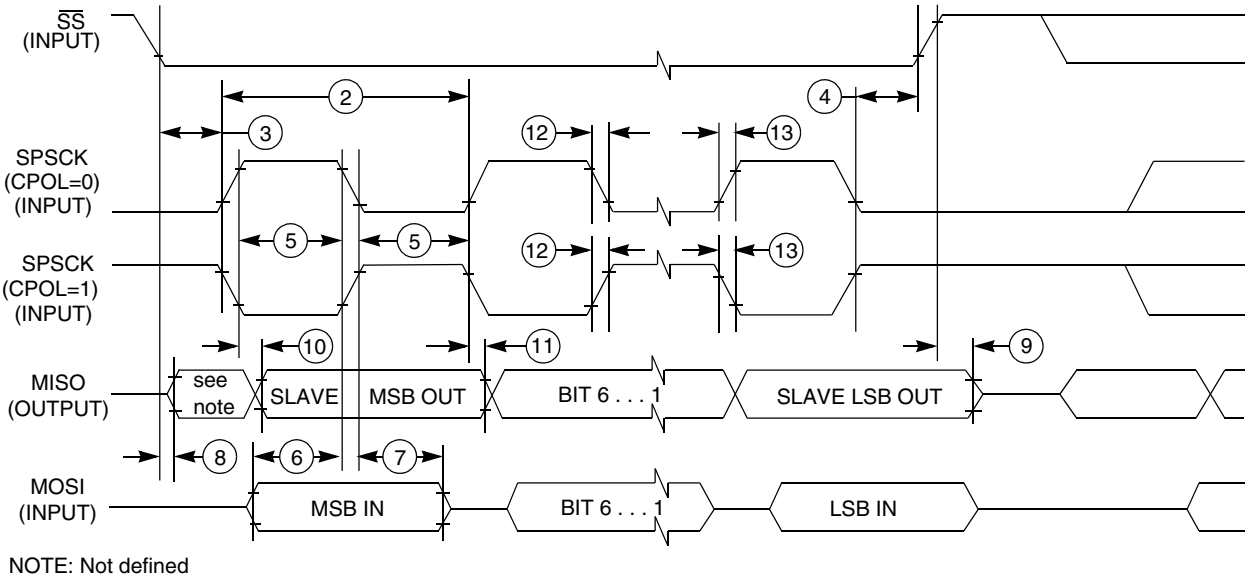


Figure 14. SPI slave mode timing (CPHA = 0)



NOTE: Not defined

Figure 15. SPI slave mode timing (CPHA = 1)

3.8.2 Inter-Integrated Circuit Interface (I2C) timing

Table 33. I2C timing

Characteristic	Symbol	Standard Mode		Fast Mode		Unit
		Minimum	Maximum	Minimum	Maximum	
SCL Clock Frequency	f_{SCL}	0	100	0	400[1]	kHz
Hold time (repeated) START condition. After this period, the first clock pulse is generated.	t_{HD}; STA	4	—	0.6	—	µs
LOW period of the SCL clock	t_{LOW}	4.7	—	1.3	—	µs
HIGH period of the SCL clock	t_{HIGH}	4	—	0.6	—	µs
Set-up time for a repeated START condition	t_{SU}; STA	4.7	—	0.6	—	µs
Data hold time for I^2C bus devices	t_{HD}; DAT	0[2]	3.45[3]	0[4]	0.9[2]	µs
Data set-up time	t_{SU}; DAT	250[5]	—	100[3, 6]	—	ns
Rise time of SDA and SCL signals	t_r	—	1000	20 +0.1C_b[7]	300	ns
Fall time of SDA and SCL signals	t_f	—	300	20 +0.1C_b[6]	300	ns
Set-up time for STOP condition	t_{SU}; STO	4	—	0.6	—	µs
Bus free time between STOP and START condition	t_{BUF}	4.7	—	1.3	—	µs
Pulse width of spikes that must be suppressed by the input filter	t_{SP}	N/A	N/A	0	50	ns

1. The maximum SCL Clock Frequency in Fast mode with maximum bus loading can only achieved when using the High drive pins (see Voltage and current operating behaviors) or when using the Normal drive pins and VDD ≥ 2.7 V

2. The master mode I^2C deasserts ACK of an address byte simultaneously with the falling edge of SCL. If no slaves acknowledge this address byte, then a negative hold time can result, depending on the edge rates of the SDA and SCL lines.
3. The maximum tHD; DAT must be met only if the device does not stretch the LOW period (tLOW) of the SCL signal.
4. Input signal Slew = 10 ns and Output Load = 50 pF
5. Set-up time in slave-transmitter mode is 1 IPBus clock period, if the TX FIFO is empty.
6. A Fast mode I^2C bus device can be used in a Standard mode I2C bus system, but the requirement $t_{SU;\ DAT} \geq 250$ ns must then be met. This is automatically the case if the device does not stretch the LOW period of the SCL signal. If such a device does stretch the LOW period of the SCL signal, then it must output the next data bit to the SDA line $t_{rmax} + t_{SU;\ DAT} = 1000 + 250 = 1250$ ns (according to the Standard mode I^2C bus specification) before the SCL line is released.
7. C_b = total capacitance of the one bus line in pF.

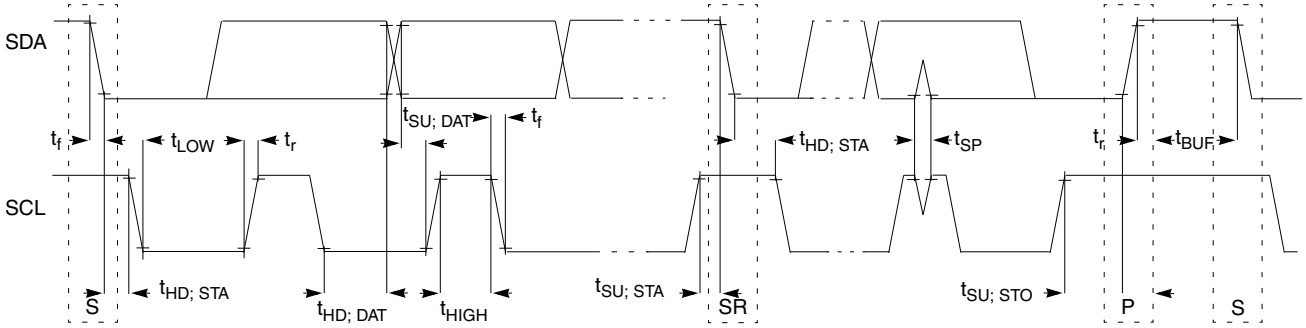


Figure 16. Timing definition for fast and standard mode devices on the I^2C bus

3.8.3 UART

See General switching specifications.

3.9 Human-machine interfaces (HMI)

3.9.1 TSI electrical specifications

Table 34. TSI electrical specifications

Symbol	Description	Min.	Typ.	Max.	Unit
TSI_RUNF	Fixed power consumption in run mode	—	100	—	µA
TSI_RUNV	Variable power consumption in run mode (depends on oscillator's current selection)	1.0	—	128	µA
TSI_EN	Power consumption in enable mode	—	100	—	µA
TSI_DIS	Power consumption in disable mode	—	1.2	—	µA
TSI_TEN	TSI analog enable time	—	66	—	µs
TSI_CREF	TSI reference capacitor	—	1.0	—	pF
TSI_DVOLT	Voltage variation of VP & VM around nominal values	0.19	—	1.03	V

4 Dimensions

4.1 Obtaining package dimensions

Package dimensions are provided in package drawings.

To find a package drawing, go to **freescale.com** and perform a keyword search for the drawing's document number:

If you want the drawing for this package	Then use this document number
24-pin QFN	98ASA00474D
32-pin QFN	98ASA00473D
32-pin LQFP	98ASH70029A
48-pin LQFP	98ASH00962A

5 Pinout

5.1 KL05 signal multiplexing and pin assignments

The following table shows the signals available on each pin and the locations of these pins on the devices supported by this document. The Port Control Module is responsible for selecting which ALT functionality is available on each pin.

48 LQFP	32 QFN	32 LQFP	24 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3
1	1	1	1	PTB6/ IRQ_2/ LPTMR0_ALT3	DISABLED	DISABLED	PTB6/ IRQ_2/ LPTMR0_ALT3	TPM0_CH3	TPM_CLKIN1
2	2	2	2	PTB7/ IRQ_3	DISABLED	DISABLED	PTB7/ IRQ_3	TPM0_CH2	
3	—	—	—	PTA14	DISABLED	DISABLED	PTA14		TPM_CLKIN0
4	—	—	—	PTA15	DISABLED	DISABLED	PTA15		CLKOUT
5	3	3	3	VDD	VDD	VDD			
6	4	4	3	VREFH	VREFH	VREFH			
7	5	5	4	VREFL	VREFL	VREFL			
8	6	6	4	VSS	VSS	VSS			

48 LQFP	32 QFN	32 LQFP	24 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3
9	7	7	5	PTA3	EXTAL0	EXTAL0	PTA3	I2C0_SCL	I2C0_SDA
10	8	8	6	PTA4/ LLWU_P0	XTAL0	XTAL0	PTA4/ LLWU_P0	I2C0_SDA	I2C0_SCL
11	—	—	—	VSS	VSS	VSS			
12	—	—	—	PTB18	DISABLED	DISABLED	PTB18		
13	—	—	—	PTB19	DISABLED	DISABLED	PTB19		
14	9	9	7	PTA5/ LLWU_P1/ RTC_CLK_IN	DISABLED	DISABLED	PTA5/ LLWU_P1/ RTC_CLK_IN	TPM0_CH5	SPI0_SS_b
15	10	10	8	PTA6/ LLWU_P2	DISABLED	DISABLED	PTA6/ LLWU_P2	TPM0_CH4	SPI0_MISO
16	11	11	—	PTB8	ADC0_SE11	ADC0_SE11	PTB8	TPM0_CH3	
17	12	12	—	PTB9	ADC0_SE10	ADC0_SE10	PTB9	TPM0_CH2	
18	—	—	—	PTA16/ IRQ_4	DISABLED	DISABLED	PTA16/ IRQ_4		
19	—	—	—	PTA17/ IRQ_5	DISABLED	DISABLED	PTA17/ IRQ_5		
20	—	—	—	PTA18/ IRQ_6	DISABLED	DISABLED	PTA18/ IRQ_6		
21	13	13	9	PTB10	ADC0_SE9/ TSI0_IN7	ADC0_SE9/ TSI0_IN7	PTB10	TPM0_CH1	
22	14	14	10	PTB11	ADC0_SE8/ TSI0_IN6	ADC0_SE8/ TSI0_IN6	PTB11	TPM0_CH0	
23	15	15	11	PTA7/ IRQ_7/ LLWU_P3	ADC0_SE7/ TSI0_IN5	ADC0_SE7/ TSI0_IN5	PTA7/ IRQ_7/ LLWU_P3	SPI0_MISO	SPI0_MOSI
24	16	16	12	PTB0/ IRQ_8/ LLWU_P4	ADC0_SE6/ TSI0_IN4	ADC0_SE6/ TSI0_IN4	PTB0/ IRQ_8/ LLWU_P4	EXTRG_IN	SPI0_SCK
25	17	17	13	PTB1/ IRQ_9	ADC0_SE5/ TSI0_IN3/ DAC0_OUT/ CMP0_IN3	ADC0_SE5/ TSI0_IN3/ DAC0_OUT/ CMP0_IN3	PTB1/ IRQ_9	UART0_TX	UART0_RX
26	18	18	14	PTB2/ IRQ_10/ LLWU_P5	ADC0_SE4/ TSI0_IN2	ADC0_SE4/ TSI0_IN2	PTB2/ IRQ_10/ LLWU_P5	UART0_RX	UART0_TX
27	19	19	15	PTA8	ADC0_SE3/ TSI0_IN1	ADC0_SE3/ TSI0_IN1	PTA8		
28	20	20	16	PTA9	ADC0_SE2/ TSI0_IN0	ADC0_SE2/ TSI0_IN0	PTA9		
29	—	—	—	PTB20	DISABLED	DISABLED	PTB20		
30	—	—	—	VSS	VSS	VSS			
31	—	—	—	VDD	VDD	VDD			
32	—	—	—	PTB14/ IRQ_11	DISABLED	DISABLED	PTB14/ IRQ_11	EXTRG_IN	

48 LQFP	32 QFN	32 LQFP	24 QFN	Pin Name	Default	ALT0	ALT1	ALT2	ALT3
33	21	21	—	PTA10/ IRQ_12	DISABLED	TSI0_IN11	PTA10/ IRQ_12		
34	22	22	—	PTA11/ IRQ_13	DISABLED	TSI0_IN10	PTA11/ IRQ_13		
35	23	23	17	PTB3/ IRQ_14	DISABLED	DISABLED	PTB3/ IRQ_14	I2C0_SCL	UART0_TX
36	24	24	18	PTB4/ IRQ_15/ LLWU_P6	DISABLED	DISABLED	PTB4/ IRQ_15/ LLWU_P6	I2C0_SDA	UART0_RX
37	25	25	19	PTB5/ IRQ_16	NMI_b	ADC0_SE1/ CMP0_IN1	PTB5/ IRQ_16	TPM1_CH1	NMI_b
38	26	26	20	PTA12/ IRQ_17/ LPTMR0_ALT2	ADC0_SE0/ CMP0_IN0	ADC0_SE0/ CMP0_IN0	PTA12/ IRQ_17/ LPTMR0_ALT2	TPM1_CH0	TPM_CLKIN0
39	27	27	—	PTA13	TSI0_IN9	TSI0_IN9	PTA13		
40	28	28	—	PTB12	TSI0_IN8	TSI0_IN8	PTB12		
41	—	—	—	PTA19	DISABLED	DISABLED	PTA19		SPI0_SS_b
42	—	—	—	PTB15	DISABLED	DISABLED	PTB15	SPI0_MOSI	SPI0_MISO
43	—	—	—	PTB16	DISABLED	DISABLED	PTB16	SPI0_MISO	SPI0_MOSI
44	—	—	—	PTB17	DISABLED	DISABLED	PTB17	TPM_CLKIN1	SPI0_SCK
45	29	29	21	PTB13	ADC0_SE13	ADC0_SE13	PTB13	TPM1_CH1	RTC_CLKOUT
46	30	30	22	PTA0/ IRQ_0/ LLWU_P7	SWD_CLK	ADC0_SE12/ CMP0_IN2	PTA0/ IRQ_0/ LLWU_P7	TPM1_CH0	SWD_CLK
47	31	31	23	PTA1/ IRQ_1/ LPTMR0_ALT1	RESET_b	DISABLED	PTA1/ IRQ_1/ LPTMR0_ALT1	TPM_CLKIN0	RESET_b
48	32	32	24	PTA2	SWD_DIO	DISABLED	PTA2	CMP0_OUT	SWD_DIO

5.2 KL05 pinouts

The following figures show the pinout diagrams for the devices supported by this document. Many signals may be multiplexed onto a single pin. To determine what signals can be used on which pin, see KL05 signal multiplexing and pin assignments.

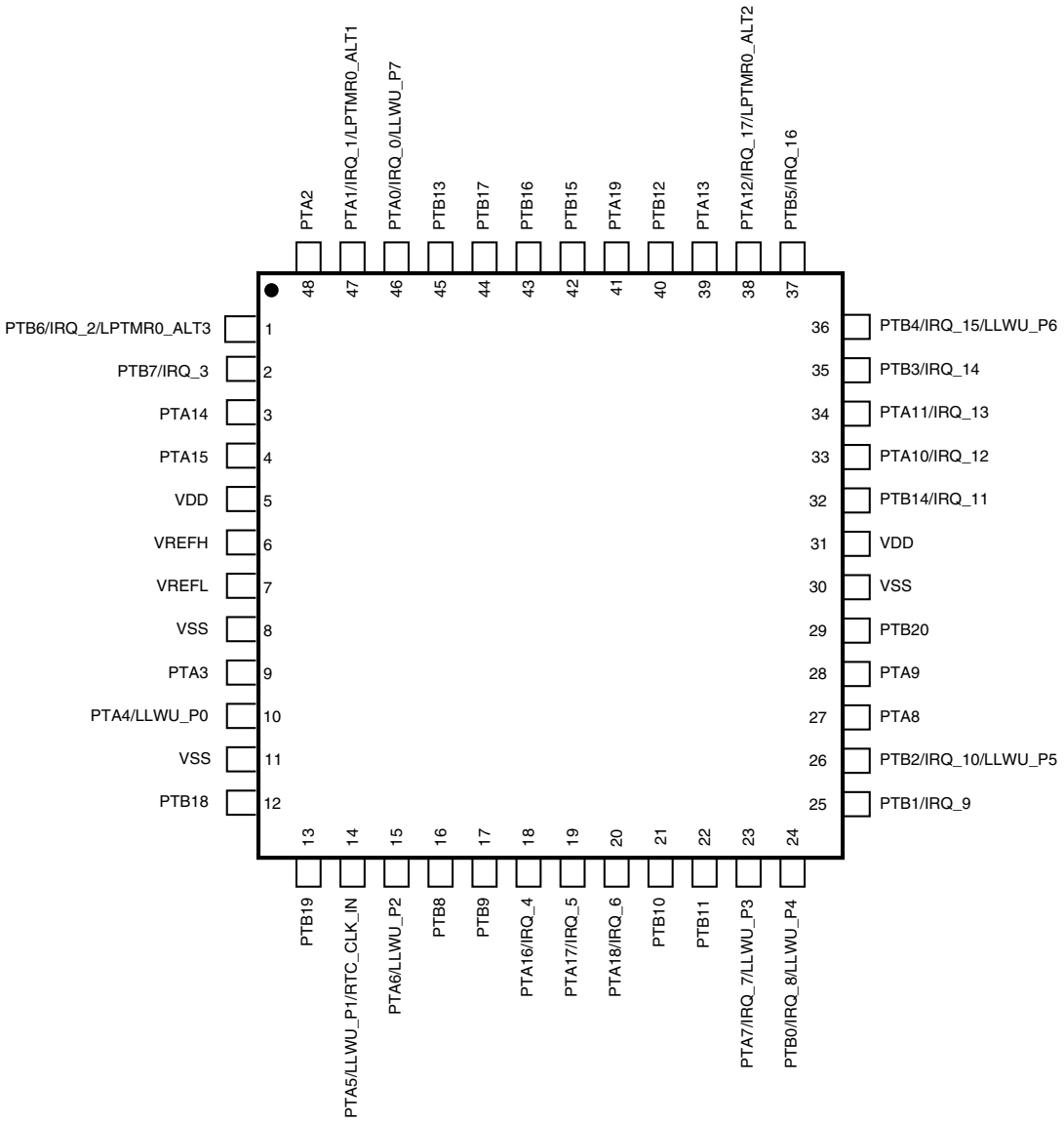


Figure 17. KL05 48-pin LQFP pinout diagram

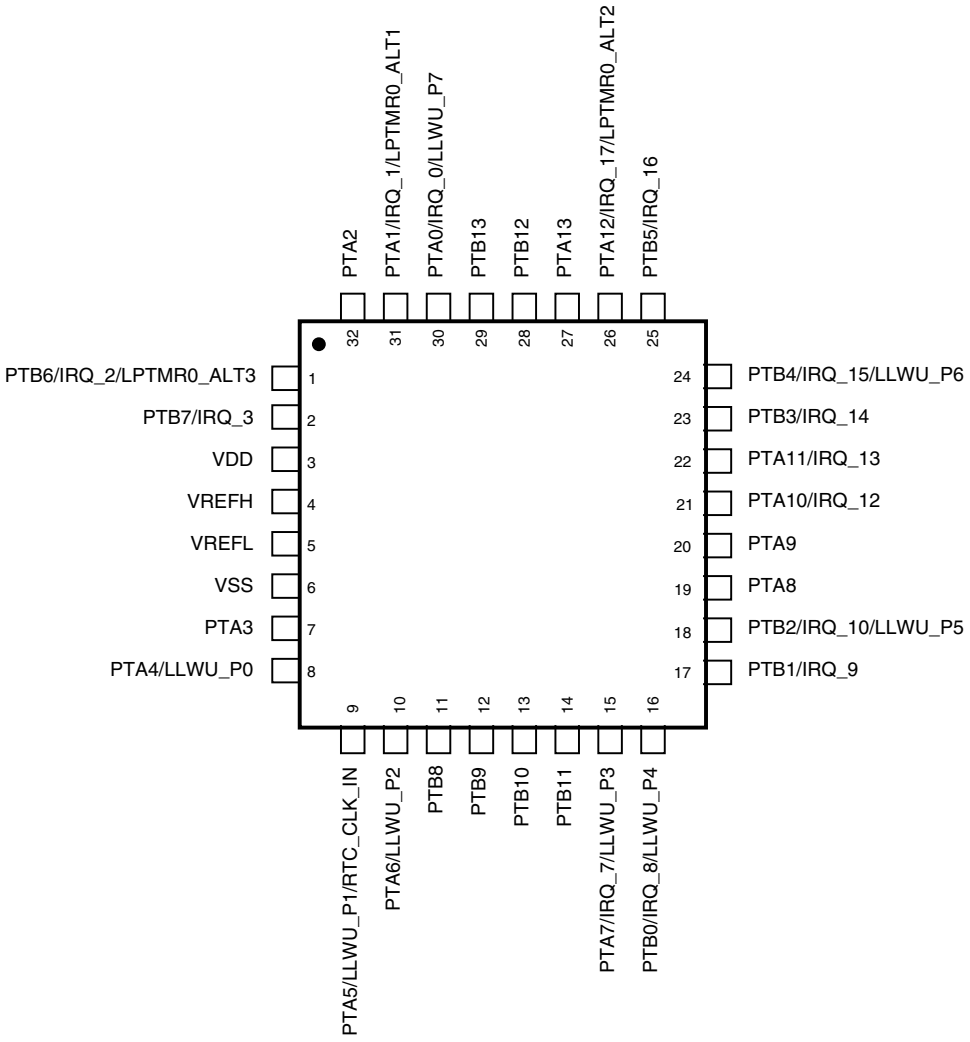


Figure 18. KL05 32-pin LQFP pinout diagram

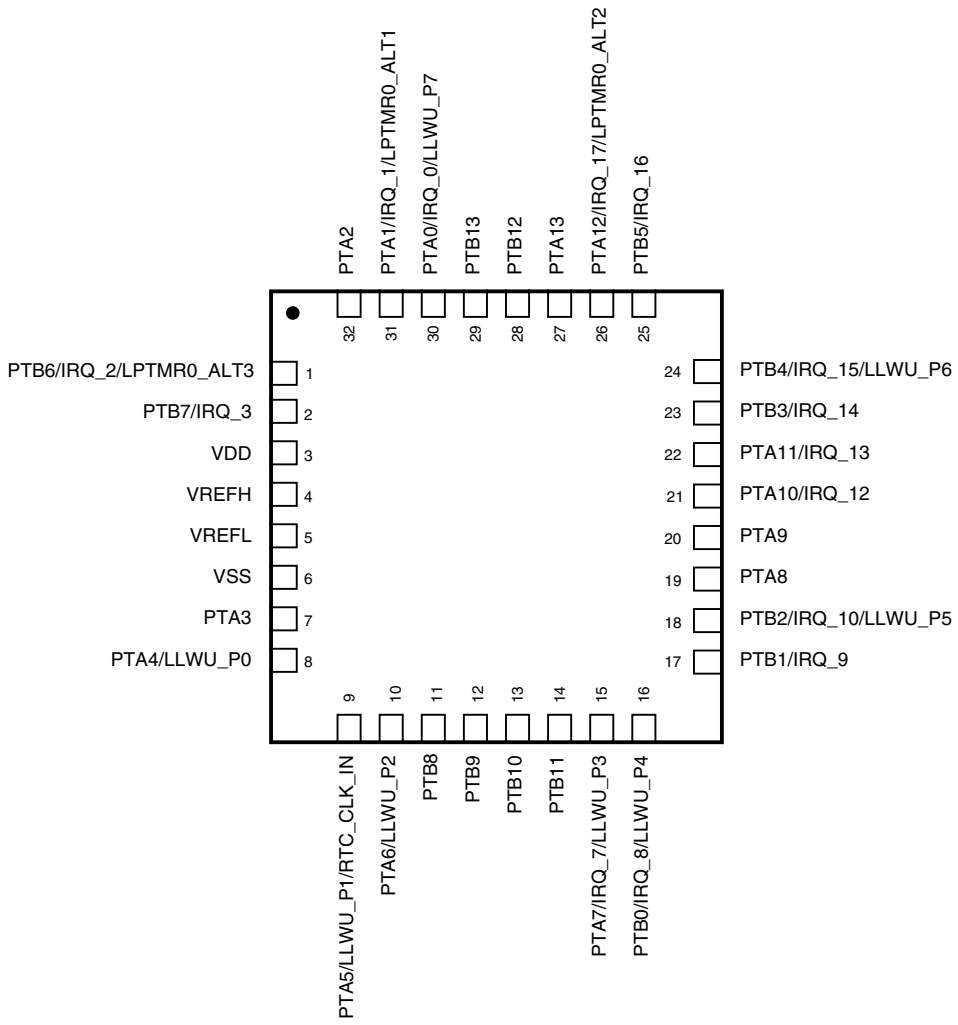


Figure 19. KL05 32-pin QFN pinout diagram

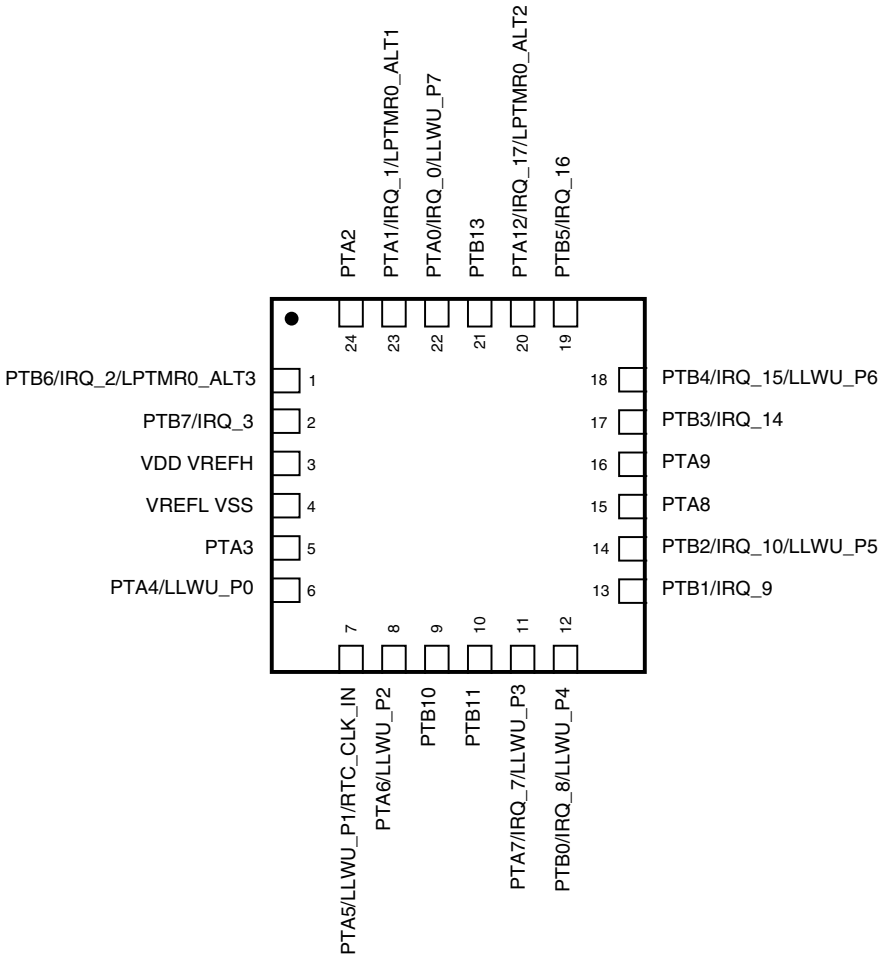


Figure 20. KL05 24-pin QFN pinout diagram

6 Ordering parts

6.1 Determining valid orderable parts

Valid orderable part numbers are provided on the web. To determine the orderable part numbers for this device, go to **freescale.com** and perform a part number search for the following device numbers: PKL05 and MKL05

7 Part identification

7.1 Description

Part numbers for the chip have fields that identify the specific part. You can use the values of these fields to determine the specific part you have received.

7.2 Format

Part numbers for this device have the following format:

Q KL## A FFF R T PP CC N

7.3 Fields

This table lists the possible values for each field in the part number (not all combinations are valid):

Table 35. Part number fields descriptions

Field	Description	Values
Q	Qualification status	• M = Fully qualified, general market flow • P = Prequalification
KL##	Kinetis family	• KL05
A	Key attribute	• Z = Cortex-M0+
FFF	Program flash memory size	• 8 = 8 KB • 16 = 16 KB • 32 = 32 KB
R	Silicon revision	• (Blank) = Main • A = Revision after main
T	Temperature range (°C)	• V = –40 to 105
PP	Package identifier	• FK = 24 QFN (4 mm x 4 mm) • LC = 32 LQFP (7 mm x 7 mm) • FM = 32 QFN (5 mm x 5 mm) • LF = 48 LQFP (7 mm x 7 mm)
CC	Maximum CPU frequency (MHz)	• 4 = 48 MHz
N	Packaging type	• R = Tape and reel • (Blank) = Trays

7.4 Example

This is an example part number:

8 Terminology and guidelines

8.1 Definition: Operating requirement

An *operating requirement* is a specified value or range of values for a technical characteristic that you must guarantee during operation to avoid incorrect operation and possibly decreasing the useful life of the chip.

8.1.1 Example

This is an example of an operating requirement:

Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	0.9	1.1	V

8.2 Definition: Operating behavior

Unless otherwise specified, an *operating behavior* is a specified value or range of values for a technical characteristic that are guaranteed during operation if you meet the operating requirements and any other specified conditions.

8.3 Definition: Attribute

An *attribute* is a specified value or range of values for a technical characteristic that are guaranteed, regardless of whether you meet the operating requirements.

8.3.1 Example

This is an example of an attribute:

Symbol	Description	Min.	Max.	Unit
CIN_D	Input capacitance: digital pins	—	7	pF

8.4 Definition: Rating

A *rating* is a minimum or maximum value of a technical characteristic that, if exceeded, may cause permanent chip failure:

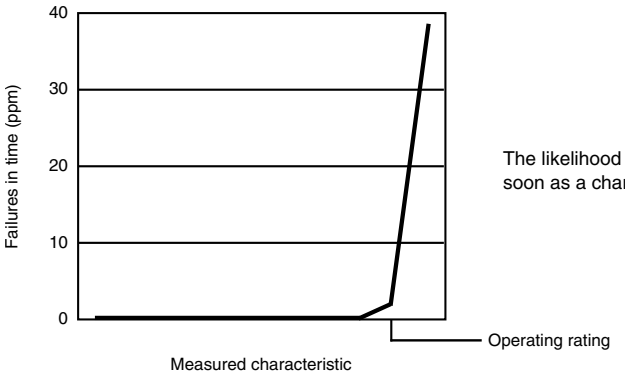
- *Operating ratings* apply during operation of the chip.
- *Handling ratings* apply when the chip is not powered.

8.4.1 Example

This is an example of an operating rating:

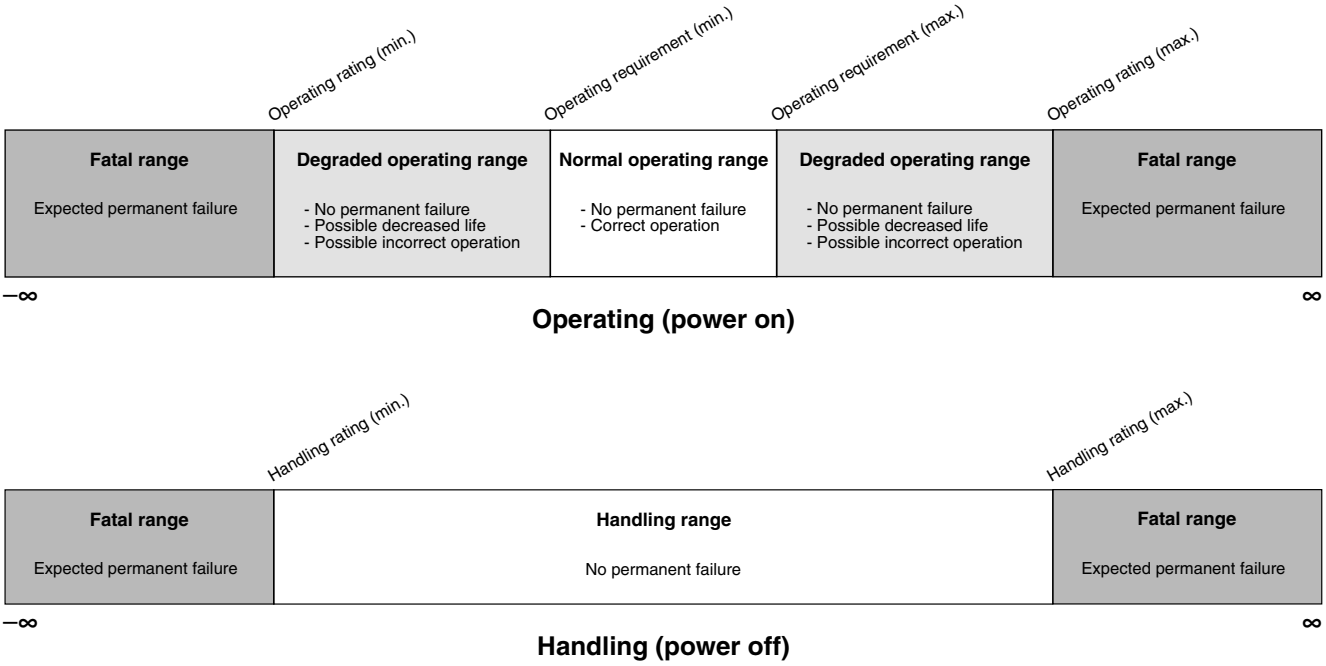
Symbol	Description	Min.	Max.	Unit
V_{DD}	1.0 V core supply voltage	–0.3	1.2	V

8.5 Result of exceeding a rating



The likelihood of permanent chip failure increases rapidly as soon as a characteristic begins to exceed one of its operating ratings.

8.6 Relationship between ratings and operating requirements



8.7 Guidelines for ratings and operating requirements

Follow these guidelines for ratings and operating requirements:

- Never exceed any of the chip's ratings.
- During normal operation, don't exceed any of the chip's operating requirements.
- If you must exceed an operating requirement at times other than during normal operation (for example, during power sequencing), limit the duration as much as possible.

8.8 Definition: Typical value

A *typical value* is a specified value for a technical characteristic that:

- Lies within the range of values specified by the operating behavior
- Given the typical manufacturing process, is representative of that characteristic during operation when you meet the typical-value conditions or other specified conditions

Typical values are provided as design guidelines and are neither tested nor guaranteed.

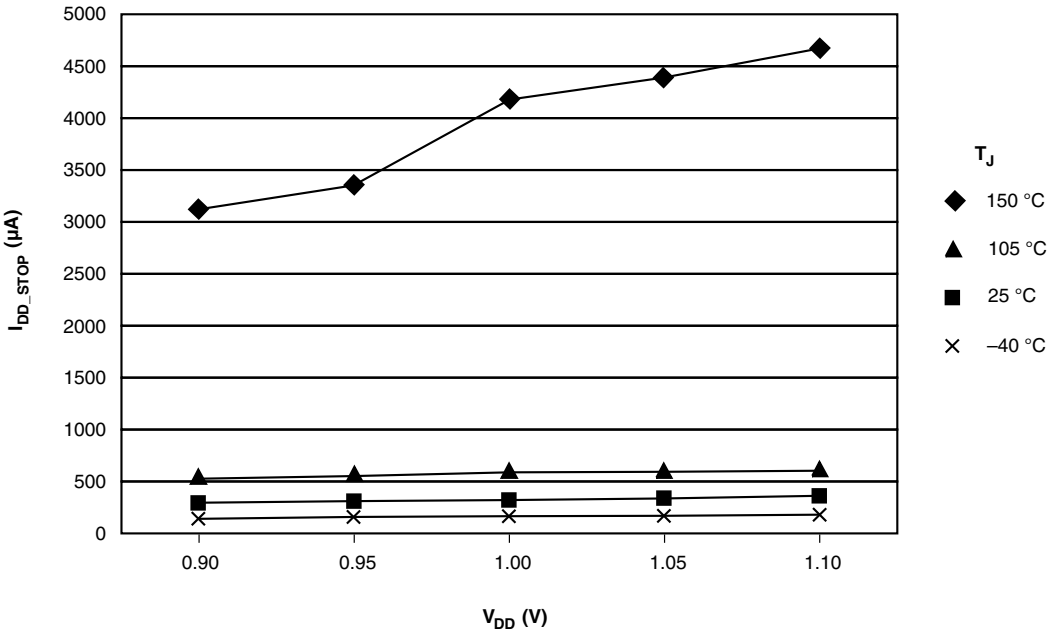
8.8.1 Example 1

This is an example of an operating behavior that includes a typical value:

Symbol	Description	Min.	Typ.	Max.	Unit
I_{WP}	Digital I/O weak pullup/pulldown current	10	70	130	µA

8.8.2 Example 2

This is an example of a chart that shows typical values for various voltage and temperature conditions:



8.9 Typical value conditions

Typical values assume you meet the following conditions (or other conditions as specified):

Table 36. Typical value conditions

Symbol	Description	Value	Unit
T_A	Ambient temperature	25	°C
V_{DD}	3.3 V supply voltage	3.3	V

9 Revision history

The following table provides a revision history for this document.

Table 37. Revision history

Rev. No.	Date	Substantial Changes
2	9/2012	Initial public release.
3	11/2012	Completed all the TBDs.
4	3/2014	• Updated the front page and restructured the chapters • Added a note to the I_{LAT} in the ESD handling ratings • Updated Voltage and current operating ratings • Added V_{ODPU} in the Voltage and current operating requirements • Updated Voltage and current operating behaviors • Updated Power mode transition operating behaviors • Updated Power consumption operating behaviors • Updated Capacitance attributes • Updated footnote in the Device clock specifications • Add $t_{hversall}$ in the Flash timing specifications — commands • Updated Temp sensor slope and voltage and added a note to them in the 12-bit ADC electrical characteristics • Removed T_A in the 12-bit DAC operating requirements • Added Inter-Integrated Circuit Interface (I2C) timing

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